

# am<sup>U</sup> CHR71000

## Datasheet

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# Table of contents

<b>1</b>	<b>General description .....</b>	<b>4</b>
1.1	Key benefits & features .....	4
1.2	Applications.....	4
1.3	Block diagram .....	5
<b>2</b>	<b>Ordering information .....</b>	<b>6</b>
<b>3</b>	<b>Pin assignment .....</b>	<b>7</b>
3.1	Pin diagram.....	7
3.2	Pin description.....	8
<b>4</b>	<b>Absolute maximum ratings .....</b>	<b>11</b>
<b>5</b>	<b>Electrical characteristics.....</b>	<b>12</b>
<b>6</b>	<b>Typical operating characteristics .....</b>	<b>13</b>
6.1	Electro-optical characteristics.....	13
6.2	Specific characteristics.....	14
<b>7</b>	<b>Functional description.....</b>	<b>19</b>
7.1	Sensor architecture .....	19
7.2	Driving the CHR71000 .....	22
7.3	Sensor timings .....	24
7.4	Windowing and subsampling .....	33
7.5	SPI programming .....	37
7.6	Reading out the sensor .....	39
<b>8</b>	<b>Register description .....</b>	<b>42</b>
8.1	Register overview.....	42
<b>9</b>	<b>Application information.....</b>	<b>46</b>
9.1	Cover glass .....	46
9.2	Color filter.....	47
<b>10</b>	<b>Package drawings.....</b>	<b>48</b>
10.1	Package .....	48

10.2	Sensor floor plan .....	49
10.3	Assembly drawing .....	50
<b>11</b>	<b>Soldering &amp; storage information .....</b>	<b>51</b>
11.1	Manual soldering .....	51
11.2	Wave soldering .....	51
11.3	Storage .....	52
11.4	Additional information .....	52
<b>12</b>	<b>Revision information .....</b>	<b>53</b>
<b>13</b>	<b>Legal information .....</b>	<b>54</b>

# CHR71000 High resolution 70 MP CMOS image sensor

## 1 General description

The CHR71000 is a High resolution 70 MP CMOS image sensor with 10000 by 7096 pixels. The image array consists of  $3.1\mu\text{m} \times 3.1\mu\text{m}$  pinned diode pixels which share a number of transistors (2 pixels sharing). The image sensor has 8 analog outputs, each running at 30MHz. The image sensor also integrates a programmable gain amplifier and offset regulation. This results in a frame rate of 3fps at full resolution. Higher frame rates can be achieved in windowing mode or subsampling mode. These and other settings are all programmable using the SPI interface. All internal exposure and read out timings are generated by a programmable on-board sequencer. External triggering and exposure programming is also possible.

### 1.1 Key benefits & features

The benefits and features of CHR71000, High resolution 70 MP CMOS image sensor are listed below:

Table 1: Added value of using CHR71000

Benefits	Features
Designed for high performance applications	A resolution of 10000×7096 pixels
Moving window	Possible to change the position of the window without intermediate register uploads
Small rolling shutter pixel	Active pixels on a $3.1\mu\text{m}$ pitch

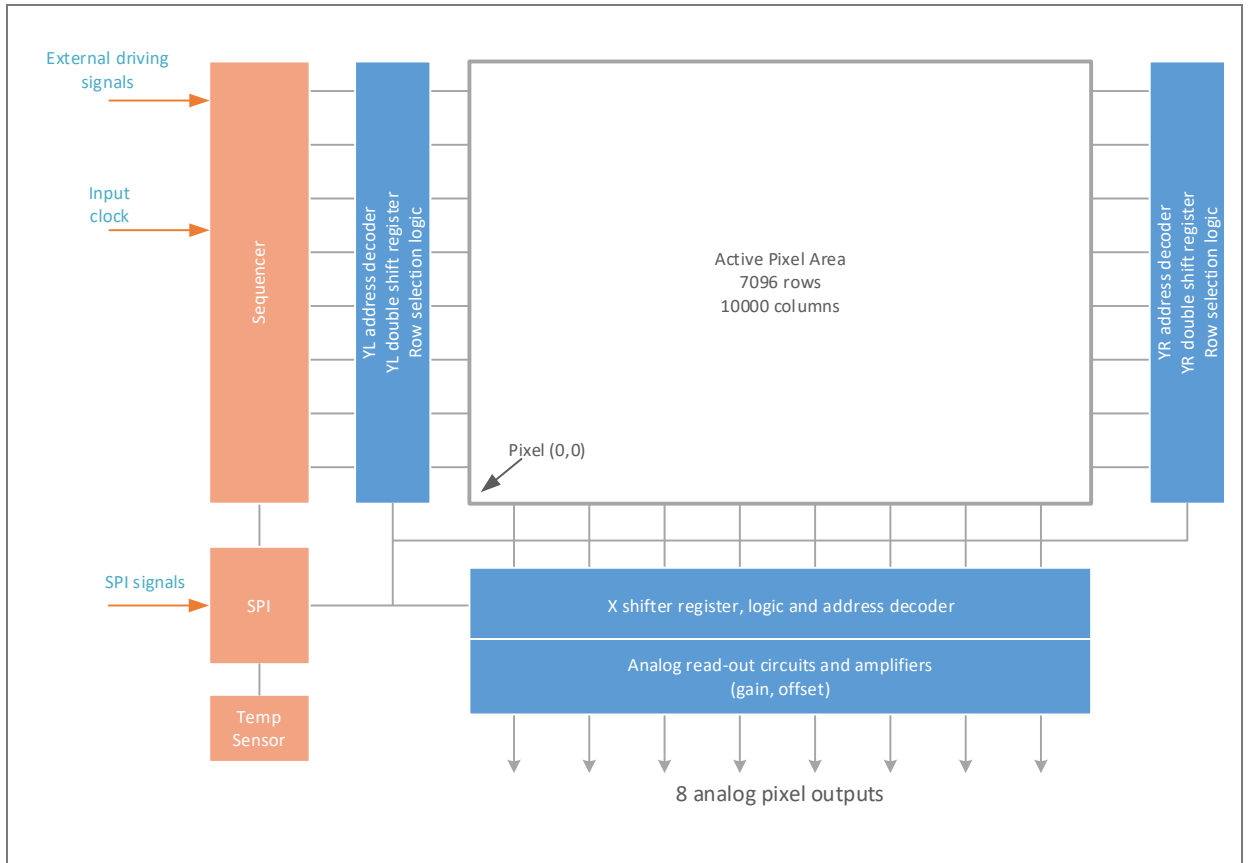
### 1.2 Applications

- Flat Panel Display Inspection
- Document Scanning
- Aerial Mapping and Surveillance

### 1.3 Block diagram

The functional blocks of this device are shown below:

Figure 1: Functional blocks of CHR71000

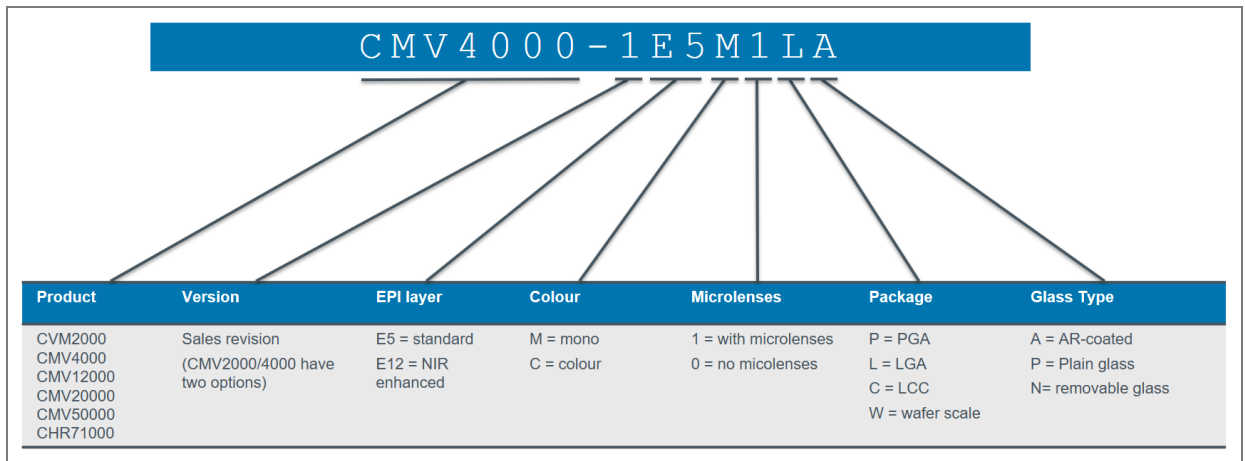


## 2 Ordering information

Product type	Ordering code	Mono/color	Glass type	Package	Delivery quantity
CHR71000ES-1E5C1PA	Q65114A0052	Color	D263 AR coated	PGA	15 pcs/tray
CHR71000ES-1E5M1PA	Q65114A0053	Mono	D263 AR coated	PGA	15 pcs/tray
CHR71000HGES-1E5M1PA <sup>(1)</sup>	Q65114A0054	Mono	D263 AR coated	PGA	15 pcs/tray

(1) High Grade variant; has no defect rows or columns.

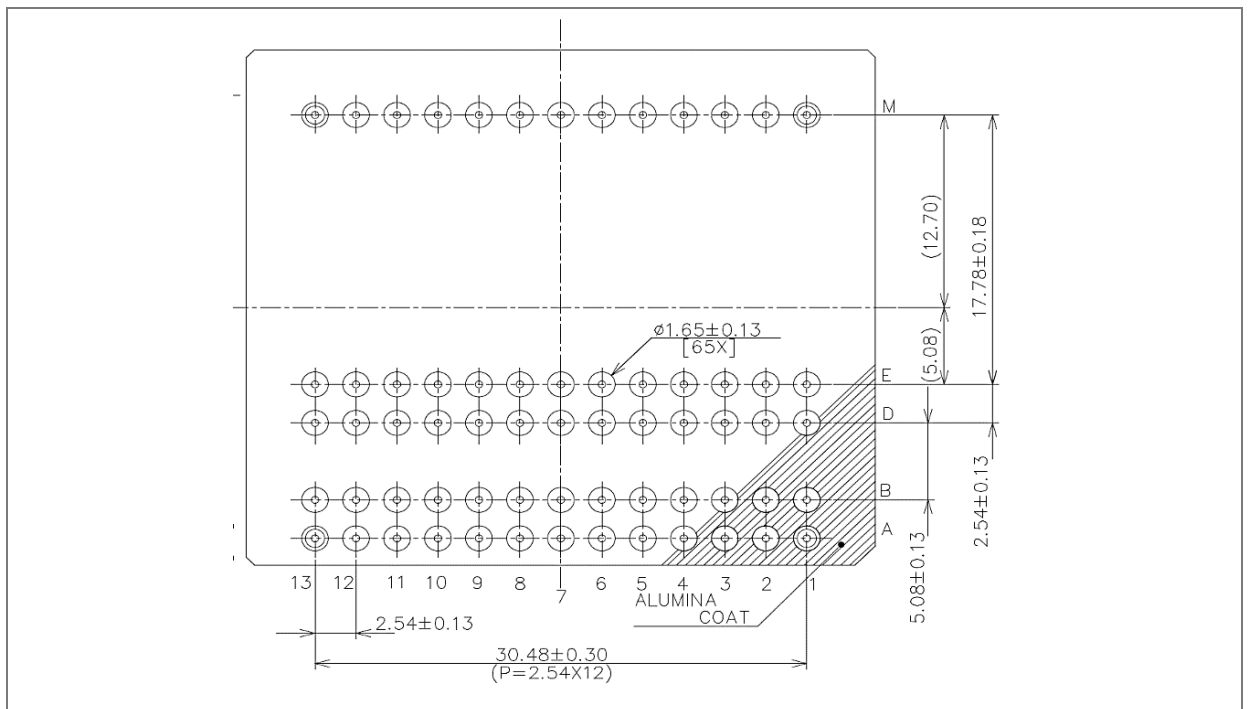
Figure 2: Product type description



### 3 Pin assignment

#### 3.1 Pin diagram

Figure 3: Pin diagram of CHR71000



## 3.2 Pin description

Table 2: Pin description of CHR71000

Pin number	Pin name	Description	Remarks
A1	CLK_IN	Master clock input	
A2	SEQ_STOP	Stop sequencer operation	
A3	OUT_LVAL	Indicates if outputs when valid (pixel signal)	
A4	SYNC_Y_READ	Sets y read shift register to start address	External signal for sequencer bypass
A5	OUT_0	Analog sensor output	Max. 20pF
A6	OUT_2	Analog sensor output	Max. 20pF
A7	OUT_4	Analog sensor output	Max. 20pF
A8	OUT_6	Analog sensor output	Max. 20pF
A9	VDD_D	Digital power supply	250mA peak current (all pins)
A10	SPI_DOUT	SPI data output (data from slave to master)	
A11	VDD_D	Digital power supply	250mA peak current (all pins)
A12	EOS_X	EOS from shift register in x direction	Not used. Do not connect.
A13	VREF	Internal bandgap reference voltage	Connect to 100nF capacitor to GND (or force bias reference voltage <sup>(1)</sup> )
B1	GND	0V reference	
B2	SYNC_X	Sets x shift register to start address	External signal for sequencer bypass
B3	OUT_CLK_SMP	Sample clock (indicates when outputs are best sampled)	
B4	SYNC_Y_INTE	Shifts input of y inte shift register at start address	External signal for sequencer bypass
B5	OUT_1	Analog sensor output	Max. 20pF
B6	OUT_3	Analog sensor output	Max. 20pF
B7	OUT_5	Analog sensor output	Max. 20pF
B8	OUT_7	Analog sensor output	Max. 20pF
B9	SPI_ENA	SPI enable signal (data transfer only valid when high)	
B10	SPI_DIN	SPI data input (data from master to slave)	
B11	GND	0V reference	
B12	PH2	Test diode, full n-well diode	Not used. Do not connect.

Pin number	Pin name	Description	Remarks
B13	DAC_LOW	DAC low reference voltage	Connect to 100nF capacitor to GND (or force bias voltage <sup>(1)</sup> )
D1	RESET_N	Global asynchronous active low reset	
D2	CLK_Y	Clock for y shift register	External signal for sequencer bypass
D3	PIX_RESET	Reset signal for pixels	External signal for sequencer bypass
D4	COL_SAMPLE	Sample signal for columns	External signal for sequencer bypass
D5	VDD_A	Analog power supply	65mA normal operation (all pins)
D6	GND	0V reference	
D7	GND	0V reference	
D8	VDD_A	Analog power supply	65mA normal operation (all pins)
D9	COL_ENABLE	Enable signal for column amplifier	External signal for sequencer bypass
D10	SPI_CLK	SPI clock input	
D11	GND	0V reference	
D12	PH1	Test diode, pixel array	Not used. Do not connect.
D13	DAC_HIGH	DAC high reference voltage	Connect to 100nF capacitor to GND (or force bias voltage <sup>(1)</sup> )
E1	SEQ_START	Start sequencer operation	
E2	PIX_TRANSFER	Transfer signal for pixels	External signal for sequencer bypass
E3	PIX_SELECT	Select signal for pixels	External signal for sequencer bypass
E4	COL_SAMPLE_R	Sample reset signal for columns	External signal for sequencer bypass
E5	COL_SAMPLE_S	Sample signal signal for columns	External signal for sequencer bypass
E6	GND	0V reference	
E7	VDD_A	Analog power supply	65mA normal operation (all pins)
E8	COL_INIT	Init signal for column amplifier	External signal for sequencer bypass
E9	COL_PRECHARGE	Precharge signal for columns	External signal for sequencer bypass
E10	CMD_COL1	Bias setting column amp 1	Connect to 100nF capacitor to VDD_ANA (or force bias voltage <sup>(1)</sup> )
E11	CMD_COL2	Bias setting column amp 2	Connect to 100nF capacitor to VDD_ANA (or force bias voltage <sup>(1)</sup> )

Pin number	Pin name	Description	Remarks
E12	CMD_OUT1	Bias setting output amp 1 (CDS/PGA)	Connect to 100nF capacitor to GND (or force bias voltage <sup>(1)</sup> )
E13	CMD_OUT2	Bias setting output amp 2 (output buffer)	Connect to 100nF capacitor to GND (or force bias voltage <sup>(1)</sup> )
M1	VDD_TRANSFER	Power supply for the transfer pixel lines	Peak current at start up <sup>(2)</sup> , 10mA peak normal operation (all pins)
M2	VDD_RESET	Power supply for the reset pixel lines	Peak current at start up <sup>(2)</sup> , 10mA peak normal operation (all pins)
M3	GNDAB	Anti-blooming supply (reset and transfer low level)	Sink current, max. 10mA (all pins). Can be tied to analog ground.
M4	EOS_Y_L_READ	EOS from left read shift register in y direction	Not used. Do not connect.
M5	EOS_Y_L_INTE	EOS from left integration shift register in y direction	Not used. Do not connect.
M6	VDD_PIX	Pixel array power supply	Has large peak currents during RBT
M7	GND	0V reference	
M8	EOS_Y_R_INTE	EOS from right integration shift register in y direction	Not used. Do not connect.
M9	EOS_Y_R_READ	EOS from right read shift register in y direction	Not used. Do not connect.
M10	CMD_COL3	Bias setting column load 1 (ctu)	Connect to 100nF capacitor to VDD_PIX (or force bias voltage <sup>(1)</sup> )
M11	CMD_COL4	Bias setting column load 2 (precharge)	Connect to 100nF capacitor to VDD_PIX (or force bias voltage <sup>(1)</sup> )
M12	VDD_PIX	Pixel array power supply	Peak currents during RBT
M13	GND	0V reference	

(1) Bias signals generated on-chip, forced outside if needed.

(2) Possibly large peak current at start-up; may be limited by resistance to pin or slower ramp-up

## 4 Absolute maximum ratings

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only. Functional operation of the device at these or any other conditions beyond those indicated under “Operating Conditions” is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 3: Absolute maximum ratings of CHR71000

Symbol	Parameter	Min	Max	Unit	Comments
<b>Continuous power dissipation (<math>T_A = 70\text{ °C}</math>)</b>					
$P_T$	Continuous power dissipation		435	mW	
<b>Electrostatic discharge</b>					
$ESD_{HBM}$	Electrostatic discharge HBM	$\pm 2000$		V	JS-001-2012 Class 2
$ESD_{CDM}$	Electrostatic discharge CDM	$\pm 250$		V	
<b>Temperature ranges and storage conditions</b>					
$T_{STRG}$	Storage temperature range	20	40	$^{\circ}\text{C}$	
$RH_{NC}$	Relative humidity (non-condensing)	30	60	%	

## 5 Electrical characteristics

All limits are guaranteed. The parameters with Min and Max values are guaranteed with production tests or SQC (Statistical Quality Control) methods.

Table 4: Electrical characteristics of CHR71000

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Power supplies</b>						
Vdd_ana	Analog read-out circuit, output amplifier			3.3		V
Vdd_dig	SPI, sequencer, row/column address logic			3.3		V
Vdd_pix	Pixel array supply			3.0		V
Vdd_AB	Anti-blooming			0 (GND)		V
Vdd_res	Pixel reset signal			3.6		V
Vdd_trans	Pixel transfer supply			3.3		V
Idd_ana	Supply current	Readout Peak		100 140		mA
Idd_dig	Supply current	Readout Peak		20 270		mA
Idd_pix	Supply current	Readout Peak		35 170		mA
Idd_res	Supply current	Readout Peak		10 70		mA
Idd_trans	Supply current	Readout Peak		10 60		mA
<b>Digital I/O</b>						
V <sub>IH</sub>	High level input voltage		2.0		Vdd_dig	V
V <sub>IL</sub>	Low level input voltage		GND		0.8	V
V <sub>OH</sub>	High level output voltage	Vdd_dig=3.3V I <sub>OH</sub> =-2mA	2.4			V
V <sub>OL</sub>	Low level output voltage	Vdd_dig=3.3V I <sub>OL</sub> =2mA			0.4	V
<b>Analog Output (OUT_x)</b>						
V <sub>OH</sub>	Output voltage high *	With gain		3.0	3.2	V
V <sub>OL</sub>	Output voltage low *	Depending on the offset	0.45		1.85	V
f					CLK_IN	MHz
C <sub>LOAD</sub>	Capacitive load drive				20	pF

## 6 Typical operating characteristics

### 6.1 Electro-optical characteristics

Below are the typical electro-optical specifications of the CHR71000. These are typical values for the whole operating temperature range unless otherwise specified.

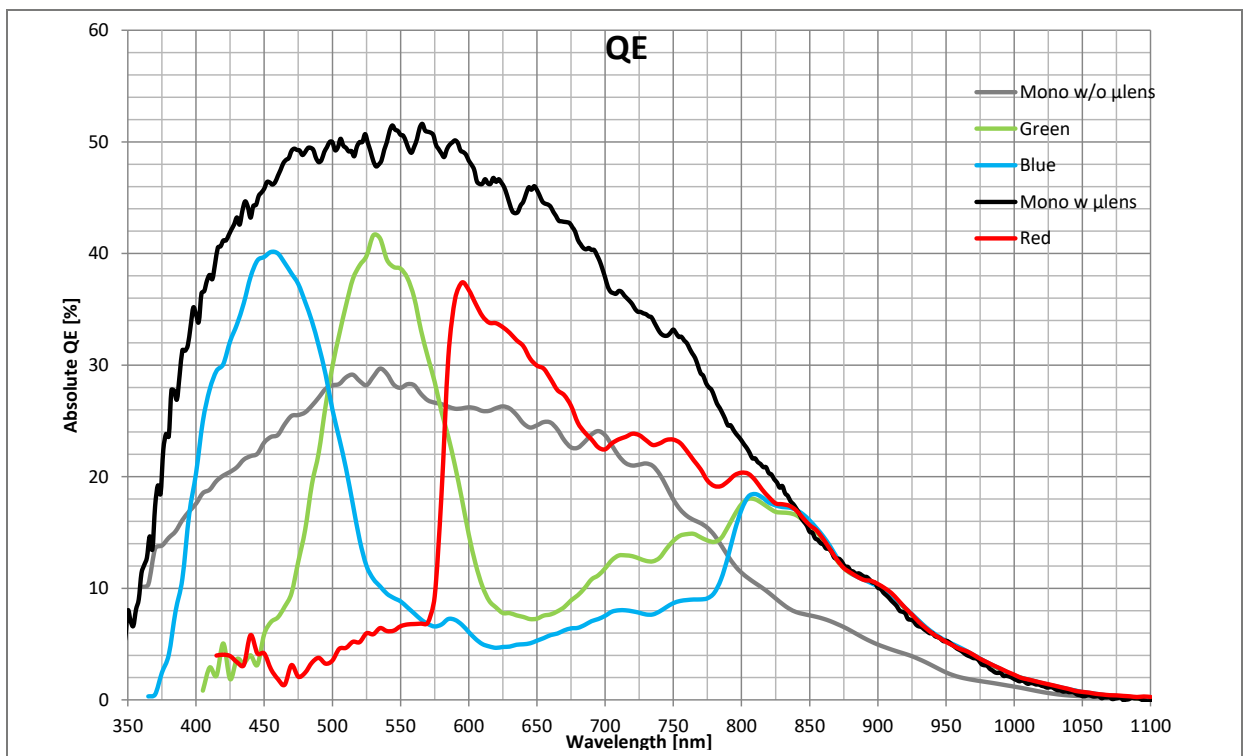
Table 5: Electro-optical characteristics

Parameter	Value	Remark
Effective pixels	10000 x 7096	10032 x 7112 including dummy pixels
Pixel pitch	3.1 x 3.1 $\mu\text{m}^2$	2-shared pixel
Full well charge	>13 ke <sup>-</sup>	Pinned photodiode pixel, two shared pixel
Signal swing	1 V	@ sensor output in lowest gain mode
Conversion gain	63 $\mu\text{V}/\text{e}^-$	@ sensor output in lowest gain
Sensitivity	0.15 A/W	@ 550nm
Temporal noise	10 e <sup>-</sup>	@ sensor output in lowest gain mode
Dynamic range	63 dB	Full well charge / temporal noise
Shutter type	Rolling shutter	With integration time control
Micro lenses	Possible	If required. 40 % gain in QE x FF expected.
Fill Factor	50 %	See comment microlenses
QE x FF	28 %	@ 550 nm, w/o microlenses
Dark current signal	3.2 e <sup>-</sup> /s	@ Room temperature
DSNU	6 e <sup>-</sup> /s	@ Room temperature
Fixed pattern noise	0.09%	% of full swing (RMS)
PRNU	1.5%	RMS
Image lag	<0.1%	
Output channels	8	8 output channels at 30 MHz
Frame rate	3 fps	@ full resolution; using a 30 MHz pixel clock
Timing generation	External (default) On-chip	Off-chip allows more flexibility but on-chip can be activated with some extent of programmability
Variable gain amplifier	x 1-4 in output stage	Programmable through SPI 16 settings
programmable registers	Sensor parameters	Window coordinates, timing parameters, gain & offset per channel, exposure times Via SPI interface.
Interface	Analog outputs	

Parameter	Value	Remark
Color filters	RGB	Bayer pattern
Package	Ceramic package	Custom PGA (65 pins)
Cover glass		Plain AR coated glass or with IR filter.
Technology	0.18 $\mu\text{m}$ CMOS	
ESD	Class 1A HBM Class 4C CDM	
RoHS	Compliant	Directive 2002/95/EC

## 6.2 Specific characteristics

Figure 4: Typical QE of a CHR71000



Below you can see the relative response of the CHR71000 with and without micro lenses. The sensors without micro lenses have a lower QE, so with the same amount of light, they will have a lower response. This is also added in to the plot below (QE-corrected curves).

This angular response is measured on the center pixels of the array where the micro-lens shift is minimal.

Figure 5: Typical spectral response of a CHR71000

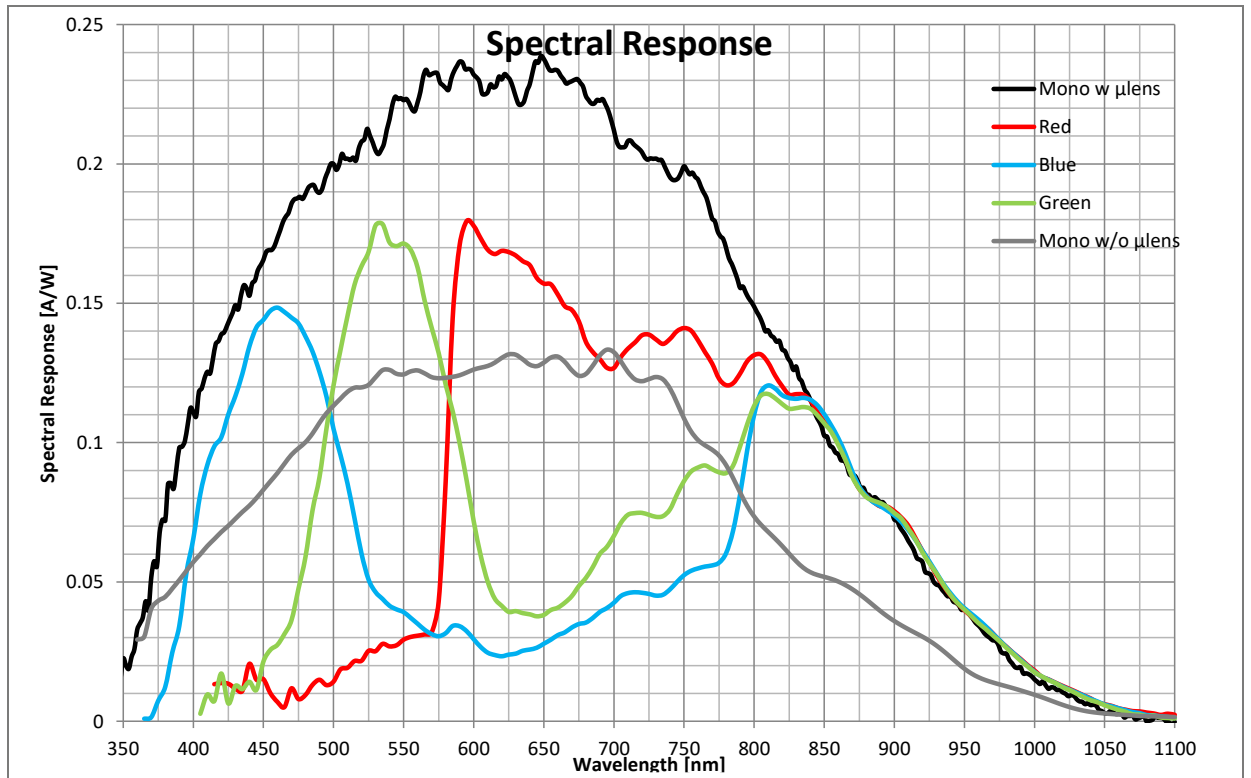
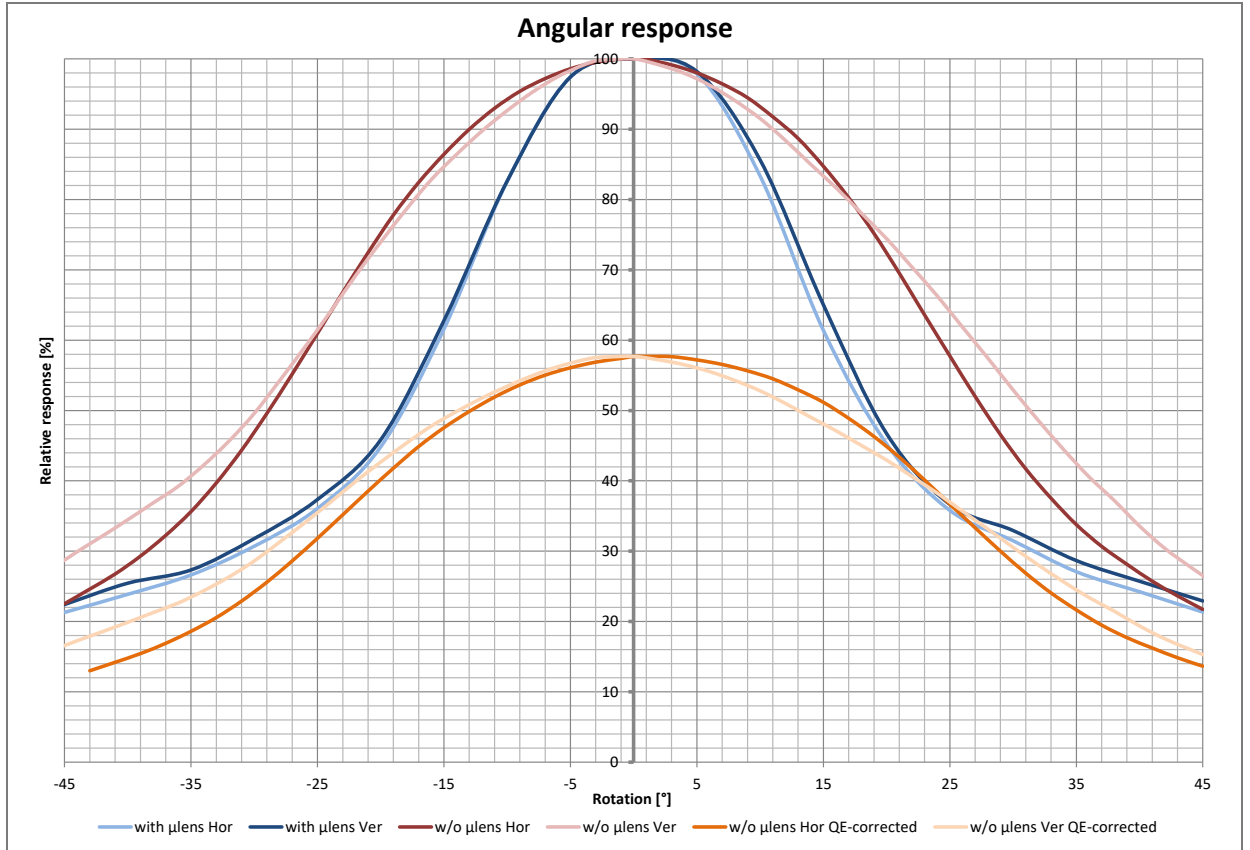


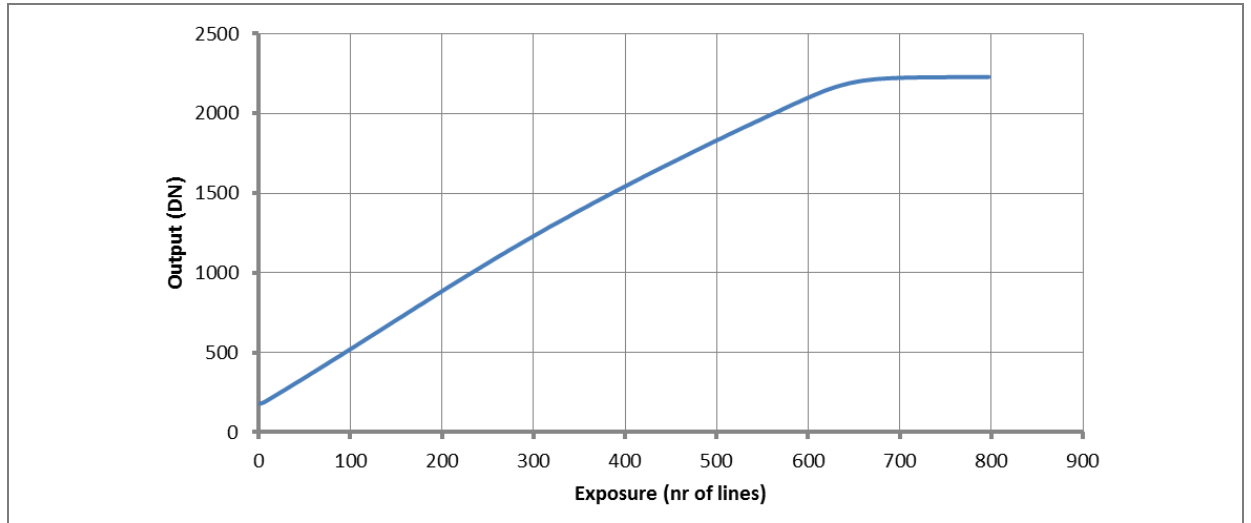
Figure 6: Angular response



### 6.2.1 Response

Figure 7 shows the typical response curve of the CHR71000 pixel.

Figure 7: Response curve of CHR71000 image sensor



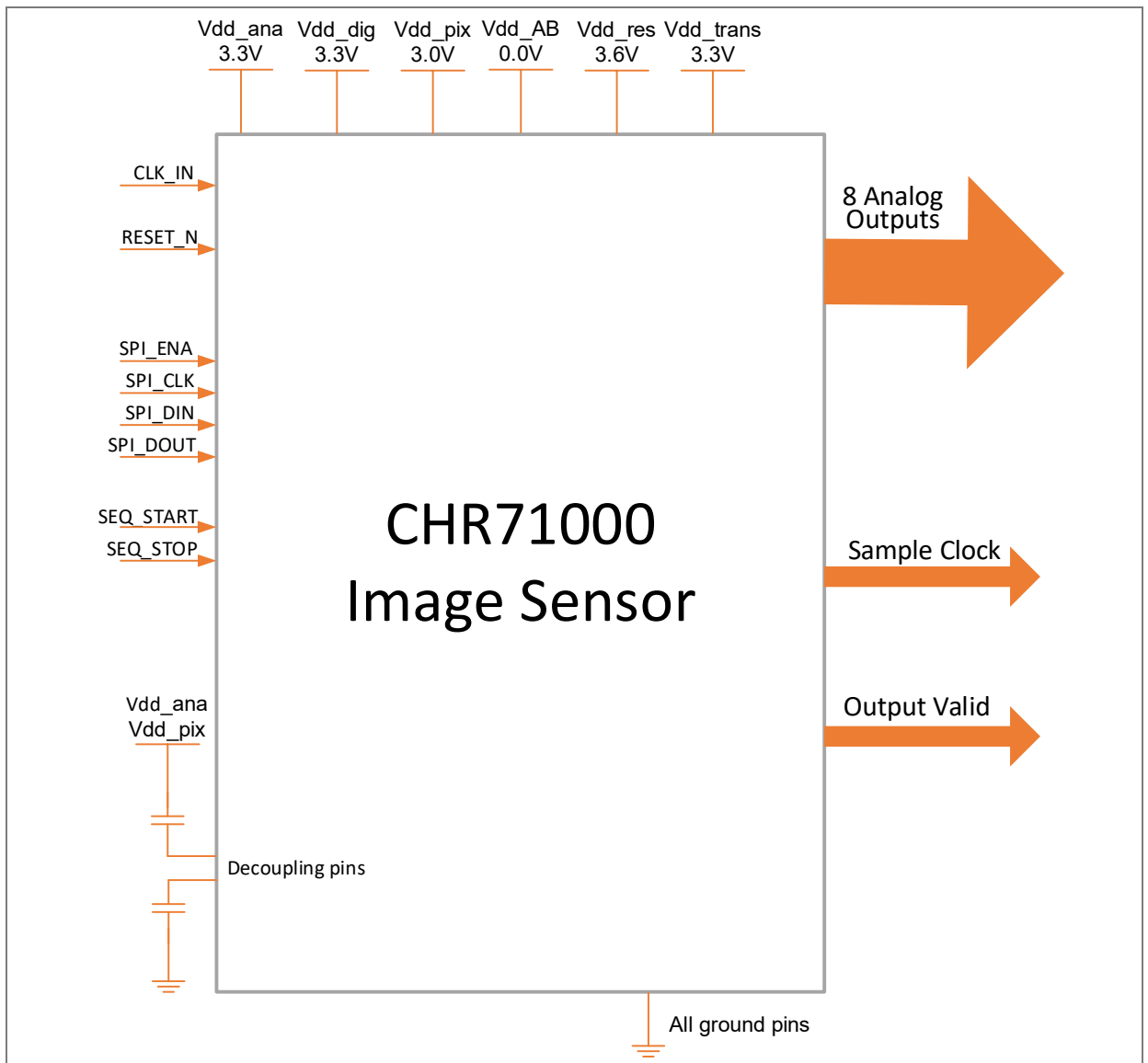


## 7 Functional description

### 7.1 Sensor architecture

Figure 10 shows the general sensor architecture. It basically consists of the pixel array, addressable shift registers in X and Y direction (for pixel read out) and column amplifiers of which the signals are multiplexed to the sensor analog outputs.

Figure 10: Connection diagram for the CHR71000 image sensor



The pixel array has 7096 rows and 10000 columns (dummy lines and columns not included) and is read out in landscape mode. The readout sequence begins by starting an integration period at the first row of the window. The address decoder is used to load pointers into the integration time shift register at the start address (writeable over SPI). The shift registers shifts its value into the next row at each `clk_Y` pulse (internally or externally generated). After the required integration time, the readout of the window is started. This is done by loading a pointer into the read shift register. This pointer is also shifted to the next row at each `clk_Y` pulse (see also 7.3.2.1). The row selection logic is equipped at both sides to speed up the row access time.

When a particular row is selected, its pixel values appear on the pixel column bus at the input of the column amplifiers. These pixel values are sampled into the sample and hold capacitors located in the column amplifier block. The column amplifier first samples the reset level of the pixel, and then, after a transfer line pulse, the photo-induced signal of the pixels is sampled.

The X shift register is then activated. Both signals are sequentially sampled over 16 multiplexed bus lines to 8 parallel output channels. Subsampling in Y can be achieved by programming the corresponding register, while 1-out-of-8 subsampling in the X direction is achieved by just sampling data from a single output channel (ignoring data from other outputs).

An SPI interface is provided to program different on-chip registers. Amongst these registers are the start and stop addresses of the window, bias settings for amplifiers, gain and offset registers of the output channels, standby of output channels, etc.

It is provided that the sensor can be fully operated by external control signals. This is a guarantee for the largest flexibility in mode of operation and possibility for full timing optimization of the different blocks. However, we have also put a sequencer on-chip that will generate all required control signals to operate the sensor from only a few external control clocks. The timing of the signals from the sequencer is based on best operation mode simulations but still quite allow some programmability. It supports full frame readout with programmable integration time, number of frames, as well as subsampled and windowed operation with possibility to move the window from frame to frame.

The default start-up condition is with external control signals. The sequencer can be activated through the SPI interface and settings of an on-chip register. At that moment, most of the external control signals are ignored and are generated by the sequencer instead.

### 7.1.1 Pixel array

The image array consists of  $3.1\mu\text{m} \times 3.1\mu\text{m}$  pinned diode pixels which share a number of transistors (2 pixels sharing) and a rolling shutter. The default product has micro lenses on top of the pixels. These lenses are shifted linearly towards the edges for a CRA of  $22.3^\circ$ .

### 7.1.2 Sequencer

It is provided that the sensor can be fully operated by external control signals (default start up condition). This is a guarantee for the largest flexibility in mode of operation and possibility for full timing optimization of the different blocks. However, we have also put a sequencer on-chip that will generate all required control signals to operate the sensor from only a few external control clocks. This sequencer can be activated through the SPI interface.

### 7.1.3 SPI interface

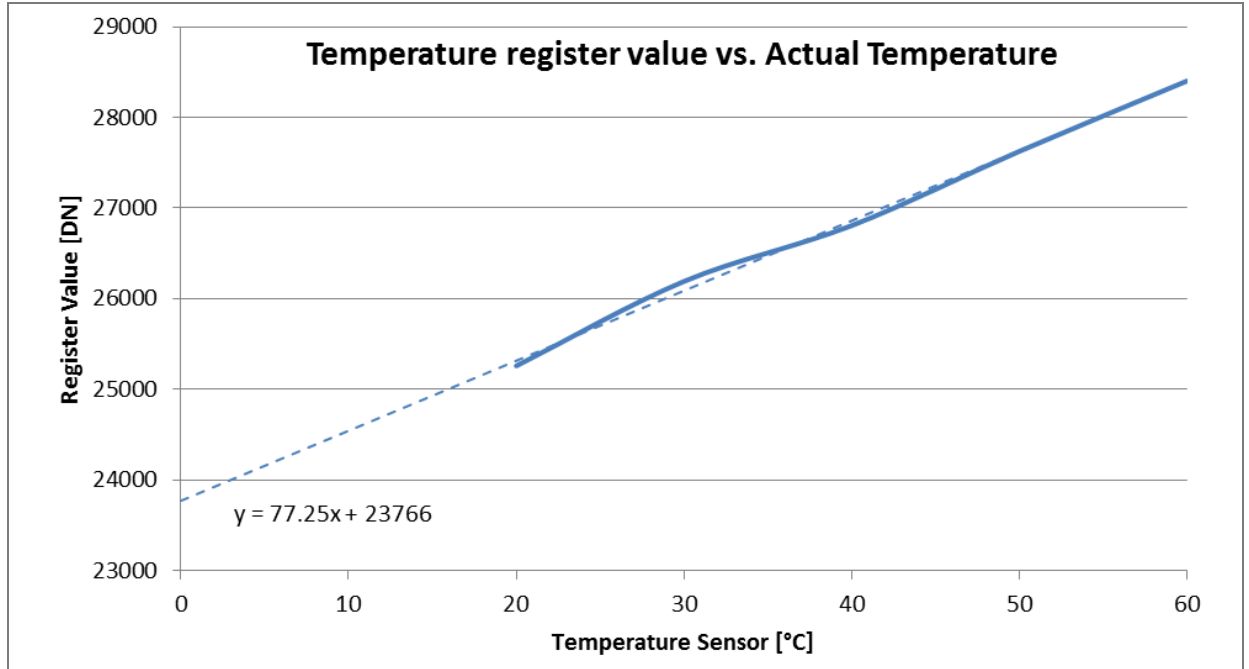
The SPI interface is used to load the sequencer registers with data. The data in these registers is used by the sequencer while driving and reading out the image sensor. Features like windowing, subsampling, gain and offset are programmed using this interface. The data in the on-chip registers can also be read back for test and debug of the surrounding system. Chapter 7.3.2.2 contains more details on register programming and SPI timing.

### 7.1.4 Temperature sensor

The on-chip temperature sensor can be read out by toggling the `reg_latch_temp_data` bit (register 125) from 1 to 0. When toggling this register like this, the temperature sensor data will be latched in registers 126-127. The temperature can then be readout by retrieving the data from the `reg_temperature` registers 126 and 127.

A calibration of the temperature sensor is needed for absolute temperature measurements as the offset between devices will vary. The temperature sensor requires a running input clock (`CLK_IN`), the other functions of the image sensor can be operational or in standby mode. The output value of the sensor is dependent on the input clock. A typical temperature sensor output vs. temperature curve at 30MHz can be found below. This results in response of about  $77 \text{ DN}/^\circ\text{C}$ .

Figure 11: Typical output of the temperature sensor of the CHR71000



## 7.2 Driving the CHR71000

The following paragraphs describe how the CHR71000 sensor can be controlled. Controlling the sensor is done in two ways:

- By applying correct timing signals to the digital input pins
- By setting the correct programmability options.

Programmability is supported by a number of on-chip registers that can be loaded with user data. The contents of these registers define the way the different blocks on the chip operate.

A digital logic block on the sensor (called 'sequencer') can be used to control the chip timing. It generates the timing pulses for the different blocks on the chip to work properly, based on settings loaded in a number of registers. It is possible to bypass the sequencer and use external pulses (digital input pins). The selection between internal or external timing can be made by register upload (see further in this chapter). The default case is external timing.

### 7.2.1 Power supplies

The CHR71000 image sensor needs six separate power supplies. Table 7 shows the typical values for the different power supplies.

The typical current is what a typical sensor draws during idle and read out. The peak currents drawn are mostly during ROT and should be countered with enough decoupling capacitors. We recommend one 100µF bulk capacitor at the regulator side and one 100nF local capacitor per supply pin (not plane!), close to the sensor pins.

### 7.2.2 Biasing

For optimal performance, some pins need to be decoupled to ground or a Vdd. Please refer to the pin list for a detailed description for every pin and the appropriate decoupling if applicable.

The table below gives an overview of the external I/O and power pins used to drive the sensor.

Table 7: Logic pins

Use	Name	Description
PWR	VDDD	Digital power
GND	VSSD	Digital ground
I	CLK_IN	Sensor master clock input
I	RESET_N	Global asynchronous active-low reset
I	SEQ_START	Start sequencer operation
I	SEQ_STOP	Stop sequencer operation
<b>Signals for sequencer bypass</b>		
I	SYNC_X	Sets x shift register to start address
I	CLK_Y	Clock for y shift register
I	SYNC_Y_READ	Sets y read shift register to start address
I	SYNC_Y_INTE	Shifts input of y inte shift register at start address
I	PIX_TRANSFER	Transfer signal for pixels
I	PIX_RESET	Reset signal for pixels
I	PIX_SELECT	Select signal for pixels
I	COL_SAMPLE	Sample signal for columns
I	COL_SAMPLE_R	Sample reset value of pixels in columns
I	COL_SAMPLE_S	Sample signal value of pixels in columns
I	COL_INIT	Initiation signal for column amplifier
I	COL_PRECHARGE	Precharge signal for columns

Use	Name	Description
I	COL_ENABLE	Enable signal for column amplifier
<b>On-chip generated signals</b>		
O	OUT_LVAL	Indicates when outputs are valid
O	OUT_CLK_SMP	Sample clock (indicates when outputs are best sampled)
<b>SPI interface signals</b>		
I	SPI_CLK	SPI clock input
I	SPI_ENA	SPI enable signal (data transfer only valid when high)
I	SPI_DIN	SPI data input (data from master to slave)
O	SPI_DOUT	SPI data output (data from slave to master)

The OUT\_LVAL and OUT\_CLK\_SMP have a driving strength to drive 30 MHz signals with a capacitive load of 20pF.

## 7.3 Sensor timings

### 7.3.1 Input clock and reset

The maximum frequency of the master clock input (CLK\_IN) is 30MHz. There are no specific duty-cycle requirements. The chip has 8 analog outputs. The frame rate is dependent of the number of lines, columns, clock frequency and the Row Overhead Time (ROT).

Equation 1:

$$line\ time = T_{CLK} * \left( ROT + \left( \frac{\#columns}{8} \right) \right)$$

Equation 2:

$$frame\ time = line\ time * \#lines$$

Equation 3:

$$frame\ rate = \frac{1}{frame\ time} = \frac{f_{CLK}}{\#lines \left( ROT + \frac{\#columns}{8} \right)}$$

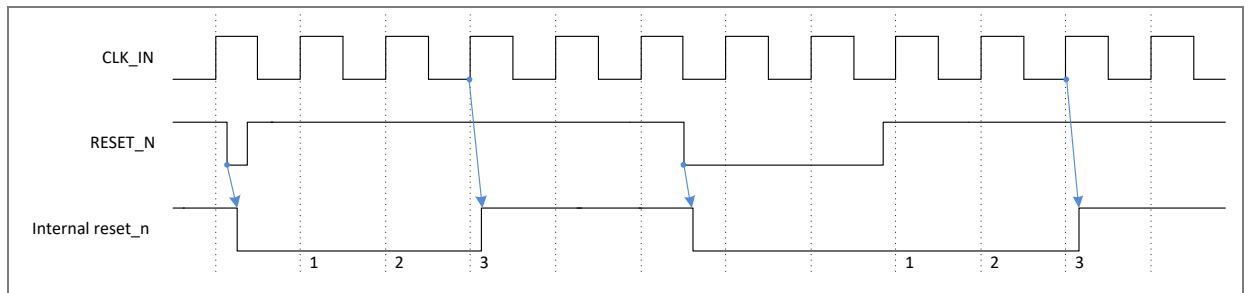
Where ROT is expressed in number of master clock periods (see point 7.3.2.2 for more details). So, for a full image with a 30MHz clock and a ROT of 168 clock cycles (default), you can achieve a 2.98fps frame rate.

The global active-low reset (RESET\_N) resets all digital sequential cells (flip-flops) in the sensor. A falling edge on the RESET\_N input (enter reset state) is fed to all sequential cells asynchronously.

A rising edge on the RESET\_N input (exit reset state) is synchronized internally to the rising edge of CLK\_IN (the 3<sup>rd</sup> one after the rising edge of the reset signal) before it goes to the flip-flops. This ensures that all flip-flops exit the reset state during the same clock period.

The reset synchronization circuit also ensures that the minimum width of an active pulse on RESET\_N is 2 clock cycles on the internal reset\_n. This means that every glitch on the RESET\_N input will generate a complete reset of the device. Figure 12 shows the timing of the reset synchronization circuit.

Figure 12: LVDS clock delay versus master clock

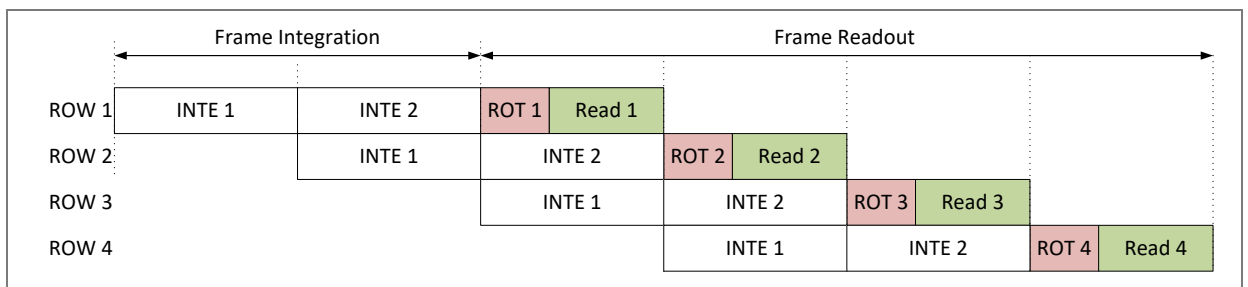


### 7.3.2 Frame and line timing

A frame is a collection of lines, which in its turn is a collection of pixels. One line-readout consists of a sampling period and a readout period. During the sampling period, all blocks on the sensor are prepared for readout of the line: the column readout structures are initialized and the pixel values (reset and signal) are copied into the columns. This operation is generally called Row Overhead Time or ROT. When the ROT has finished, the pixel values that are stored in the columns are read out sequentially. This sequence is repeated for every line in a frame.

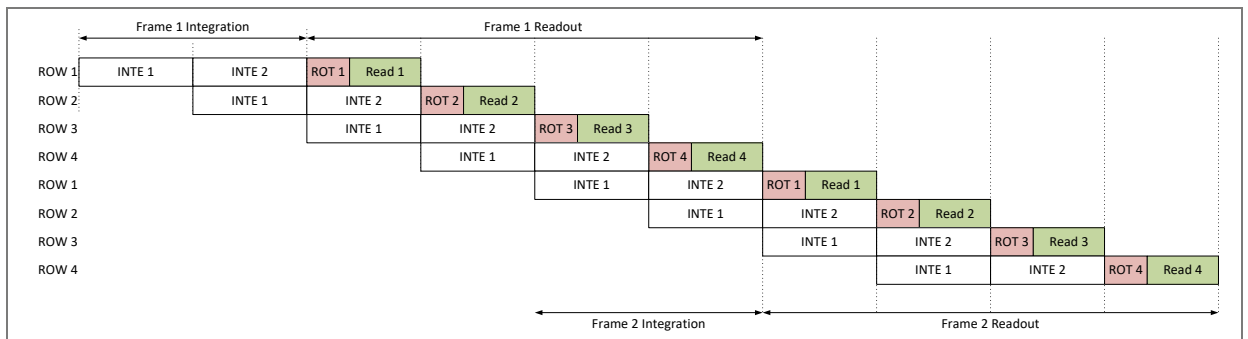
Before the readout of a frame can start, an integration period must have passed. During this period, light integrates in the pixels. The integration time is specified as a number of line times. Figure 13 shows the timing of reading out 1 frame of 4 lines with an integration time of 2 line times.

Figure 13: Schematic representation of integration and readout



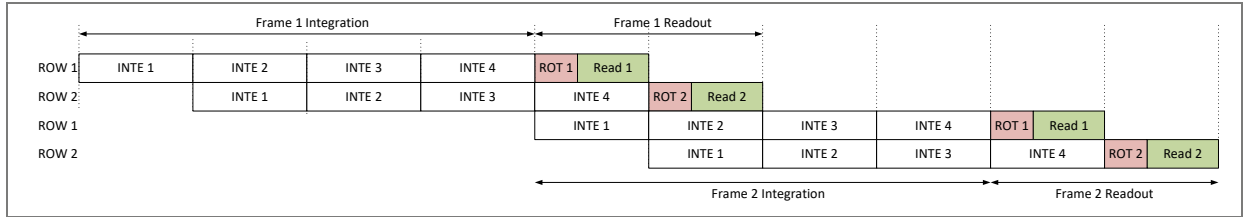
Because of the rolling shutter operation of the sensor, the integration of frame n+1 can happen during the readout of frame n. Figure 14 shows the timing of reading out 2 frames of 4 lines with an integration time of 2 line times.

Figure 14: Example of readout of 2 frames (4 lines) with 2 lines integration time



If the integration time (in number of lines) is longer than the number of lines in a frame, the start of a frame is delayed until the integration time has finished. Figure 15 shows the timing of reading out 2 frames of 2 lines, with an integration time of 4 line times.

Figure 15: Example of readout of 2 frames (2 lines) with 4 lines integration time



### 7.3.2.1 Using external timing

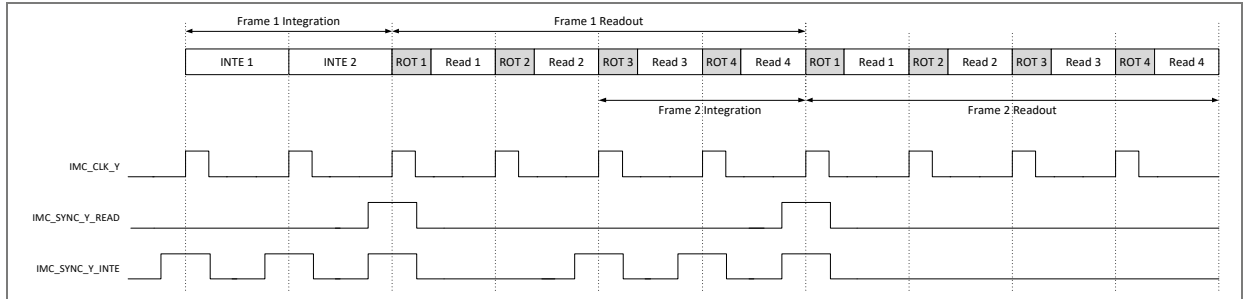
The frame timing (integration and row readout) is controlled with the signals CLK\_Y, SYNC\_Y\_READ and SYNC\_Y\_INTE. A new line time starts at every rising edge on CLK\_Y. A line time can have three functions. The function of a line is defined by the state of SYNC\_Y\_READ and SYNC\_Y\_INTE at the time of the rising edge on CLK\_Y. The three functions of a line can be:

Table 8: Line functions

SYNC_Y_READ	SYNC_Y_INTE	Function
1	1	First line of a frame read-out
0	1	Integration
0	0	Reset. A line is in reset if it is not integrating or being read-out.
1	0	Illegal

As an example, the figure showing the timing of reading out 2 frames of 4 lines with an integration time of 2 lines is repeated, but with the timing of the three input pulses, like shown on Figure 16.

Figure 16: Timing with external signals



The exact timing of these three signals and their relation to the timing of the other digital inputs is specified in more detail in section 7.3.2.2.

Because of the 4T shared pixel architecture, a number of extra rules apply to the timing of CLK\_Y, SYNC\_Y\_READ and SYNC\_Y\_INTE:

- The integration on a line can only start 2 line times after that line has been read out. This means that if the address settings are unchanged between two frames, there must be two line times with function “Reset” after the line “First line” before a line with function “Integration” can start.
- The y-start address can only change to a new value 2 line times after the line addressed by that new value has been read out.

### 7.3.2.2 Using the internal sequencer

When using the internal sequencer, all image core signals are generated on the chip. The only digital inputs that need to be driven when using the sequencer are CLK\_IN, RESET\_N, SEQ\_START and SEQ\_STOP. The SEQ\_START is pulsed to initiate a frame transfer and SEQ\_STOP can be used to stop a frame transfer before it is finished. The rest of the timing is controlled through register upload. The internal sequencer is enabled by writing a '1' to the register reg\_seq\_enable.

The most important properties that are controlled through register upload are:

- The number of frames that are grabbed after a pulse on SEQ\_START. (Set by register reg\_nrof\_frames[15:0]. The range is 1 to 65535. If a value of 0 is uploaded, the sensor sends out frames continuously until stopped by a pulse on SEQ\_STOP).
- The integration time (expressed as number of line times). (Set by register reg\_inte\_time[23:0]. The range is 1 to 224-1. A value of 0 is invalid).
- The window and sub-sampling settings. (Set with registers reg\_addr\_x\_start[9:0], reg\_addr\_y\_start[9:0], reg\_addr\_x\_end[9:0], reg\_addr\_y\_end[9:0] and reg\_sub\_y. The range of this registers has been discussed before).

The timing generated by the sequencer follows the timing as specified in previous section, with a setting of 60 clock cycles for sample length and 30 clock cycles for transfer length respectively.

### 7.3.3 Row overhead timing

During the row overhead time (ROT), the digital chip inputs need to be pulsed when the internal sequencer is not used. Figure 17 shows the required timing of the pulses and their relation to the master clock input.

The timing for the two signals `imc_sync_y_read` and `imc_sync_y_inte` is combined into one signal in the figure (`imc_sync_y_*`). The ROT length is defined in first order by the sample length and the transfer length. Next table gives the details of the programmable timing. The last column details the number of clock cycles (30MHz) for the duration of each state.

Table 9: Different programmable timings according with MCLK cycles

#	Name	From	To	Clock cycles
T1		r-edge <code>sync_y_*</code>	r-edge <code>clk_y</code>	3
T2		r-edge <code>clk_y</code>	f-edge <code>clk_y</code> f-edge <code>sync_y_*</code> f-edge <code>pix_reset</code> r-edge <code>col_enable</code>	1
T3		f-edge <code>pix_reset</code>	r-edge <code>col_precharge</code>	0
T4	Precharge length	r-edge <code>col_precharge</code>	f-edge <code>col_precharge</code>	2
T5		f-edge <code>col_precharge</code>	r-edge <code>pix_select</code> r-edge <code>col_init</code> r-edge <code>col_sample</code> r-edge <code>col-sample_r</code>	0
T6	Sample length	r-edge <code>col_sample</code>	f-edge <code>col_sample</code>	60
T7		f-edge <code>col_init</code>	f-edge <code>col_sample</code>	14
T8		f-edge <code>col_sample</code>	f-edge <code>col_sample_r/s</code> f-edge <code>pix_select</code>	1
T9		f-edge <code>pix_select</code>	r-edge <code>pix_transfer</code>	1
T10	Transfer length	r-edge <code>pix-transfer</code>	f-edge <code>pix_transfer</code>	30
T11		f-edge <code>pix_transfer</code>	r-edge <code>col_precharge</code>	1
T12		f-edge <code>pix_select</code>	r-edge <code>pix_reset</code>	1
T13		r-edge <code>pix_reset</code>	r-edge <code>sync_x</code>	1
T14		f-edge <code>col_precharge</code>	f-edge <code>col_sample</code>	46

If a value of '0' is entered for one of the registers, the state will be skipped.

Except for states T6 and T7 all states are sequential. If the value entered for T7 is larger than the value of T6, the `col_init` signal will not go to '1' during the ROT.

`IMC_COL_PRECHARGE` is not going low after T4, instead it overlaps with `IMC_COL_SAMPLE`.

The length of the ROT is  $(T1+T2+T3+2*(T4+T5+T6+T8)+T9+T10+T11+T12+T13+4)$ . With the default values, the ROT length is 168 clock cycles, or 5.56  $\mu$ s. The read out will start after this ROT (4 clock pulses after sync\_x rising edge).

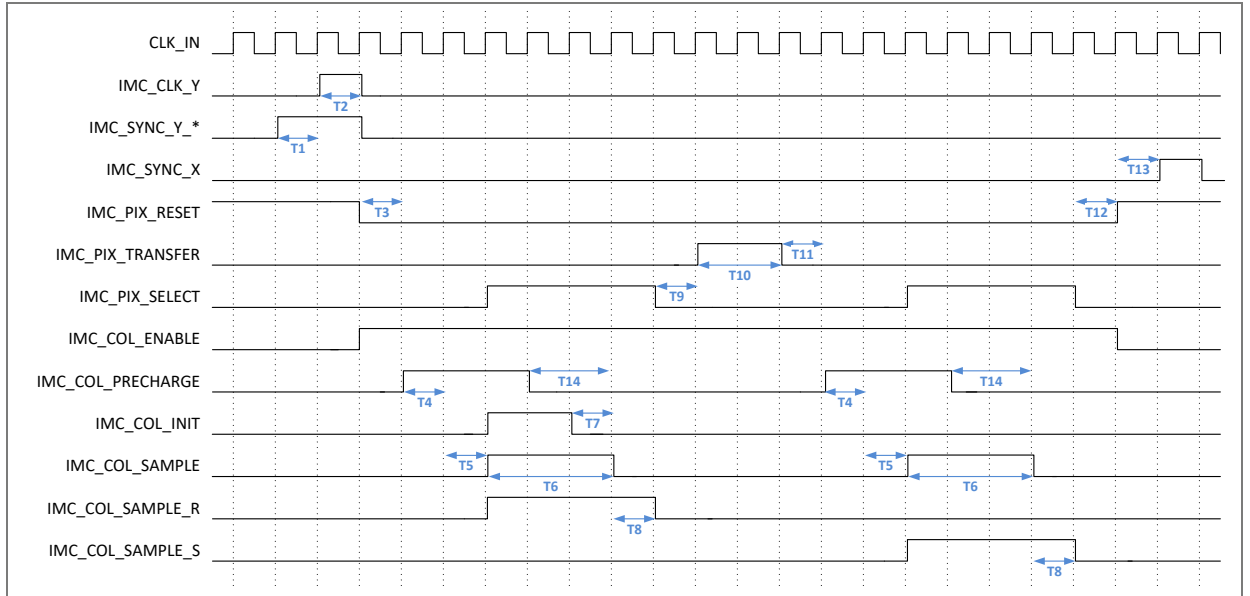
The ROT timing can be configured further with the following registers:

- With the register reg\_pol, the polarity of all outputs can be set. To achieve the timing as in previous figure, the reg\_pol bit for every signal should be '1'. The signal can be inverted by changing the register bit to '0'. Next table shows which register bit maps to which signal.

Table 10: Reg\_pol description

Reg_pol	Output
[0]	imc_sync_x
[1]	imc_clk_y
[2]	imc_sync_y_read
[3]	imc_sync_y_inte
[4]	imc_pix_transfer
[5]	imc_pix_reset
[6]	imc_pix_select
[7]	imc_col_sample
[8]	imc_col_sample_r
[9]	imc_col_sample_s
[10]	imc_col_init
[11]	imc_col_precharge
[12]	imc_col_enable

Figure 17: Timing diagram



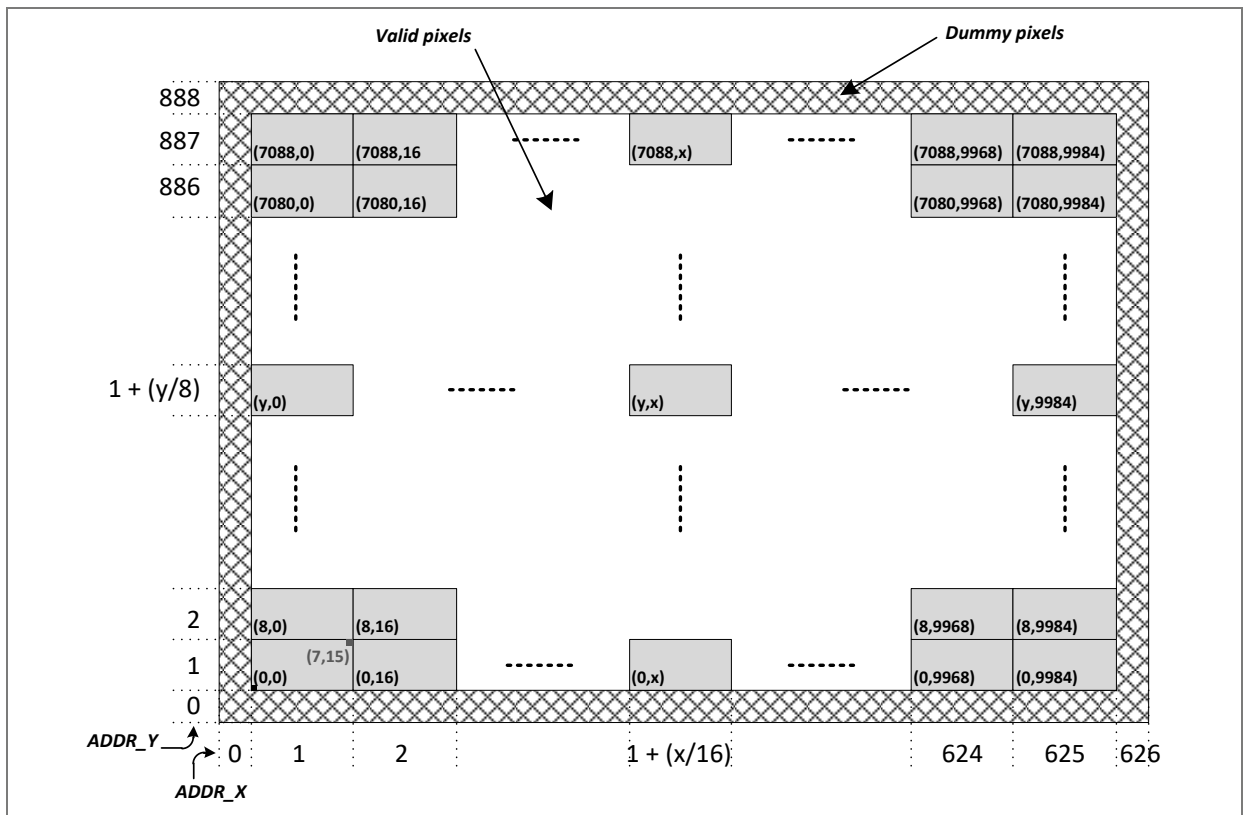
## 7.4 Windowing and subsampling

### 7.4.1 Windowing

The pixel array resolution is 10000 pixels in x direction and 7096 pixels in y direction. On each side of the pixel array, there are a number of dummy pixels (to improve the optical behavior of the pixels at the edges of the active pixel array). For windowing purposes, the rows and columns of the pixel array have an address. When reading out a frame, the start and end positions of the frame in x- and y-direction need to be specified. To reduce the number of available addresses, only every 16<sup>th</sup> column and every 8<sup>th</sup> row have an address. This means that the size of a window is always a multiple of 16(x) by 8(y) pixels.

The dummy pixels on each side of the pixel array also have an address (y,x): (0,y), (626,y), (x,0) and (x,888). Figure 18 shows a representation of the pixel array with the addresses in x and y direction.

Figure 18: Representation of the pixel array



The position of a pixel is specified as a two dimensional coordinate, written as (y,x). Pixel (0,0) is the left-bottom pixel of the valid pixel array. The valid array extends from pixel (0,0) to pixel (7095, 9999). Pixels (0,0) to (8,15) are addressed with address (1,1). From then on, the y-address increases by 1 every 8 rows and the x-address by 1 every 16 columns. This means that the address of a window with position (y,x) can be written as (  $1+(y/8)$  ,  $1+(x/16)$  ).

The window that is read out is defined by the four 10-bit registers `reg_addr_x_start`, `reg_addr_x_end`, `reg_addr_y_start` and `reg_addr_y_end` (see later for more details on programmability). The registers `reg_addr_x_start` and `reg_addr_y_start` point at the first column and row of the window. The registers `reg_addr_x_end` and `reg_addr_y_end` point at the first column and row that are outside the window at its right-top corner.

Example: To read out a 128(y)\*64(x) window starting from pixel (24,32):

- The window is between pixels (24,32) and (151,95)
- The address of the first pixel of the window (24,32) maps to address (4,3)
- The address of the first pixel outside of the window (152,96) maps to address (20,7)
- Upload the following values:
  - `reg_addr_x_start` = 3
  - `reg_addr_x_end` = 7
  - `reg_addr_y_start` = 4
  - `reg_addr_y_end` = 20

A full frame readout (pixel (0,0) to pixel (7095,9999)) requires the following values:

- `reg_addr_x_start` = 1
- `reg_addr_x_end` = 626
- `reg_addr_y_start` = 1
- `reg_addr_y_end` = 888

## 7.4.2 Moving window

It is possible to change the position of the window every subsequent frame without intermediate register uploads. The window can be moved by setting the registers `reg_addr_x_step` and `reg_addr_y_step`. If they are both set to 0, the window does not move. If one of the registers is set to a non-zero value, the window moves in that direction. If both are set, the window moves diagonally.

Window stepping is only allowed if the number of frames is constrained. If the `reg_nrof_frames` register is set to 0 (continuous frames), the value in the 'step' registers is ignored.

The `reg_addr_x/y_step` registers are 10-bit wide and represent a signed integer. This allows stepping in both positive and negative directions (the window can move up-left, left, down-left, down, down-right, right, up-right and up). These registers have the same behavior as the windowing registers (steps of 8 and 16).

Table 11: Moving window setting

10-bit	Int	Signed int
00 0000 0000	0	0
00 0000 0001	1	1
...		
01 1111 1111	511	511
10 0000 0000	512	-512
10 0000 0001	513	-511
...		
11 1111 1111	1023	-1

If invalid frame settings are set in moving window mode (addresses out of range), frame grabbing is aborted at the start of the next frame and the sensor will return to idle mode.

### 7.4.3 Subsampling

Next to windowing, the sensor also supports sub-sampling in y. Sub-sampling in y can be enabled with a register upload (it's off by default). When sub-sampling is enabled, only every 8th row is read out. The window size in y is divided by 8. Sub-sampling is not possible in the x-direction because of the parallel output structure (8 columns read out in parallel). Sub-sampling in x-direction is actually achieved by ignoring data on some outputs (these outputs can be put in standby in such case).



#### Information:

- Note that the integration time is specified as a number of line times. If the window size in x is changed, the time it takes to read out a line also changes. This means that changing the window size in x also changes the actual integration time.

### 7.4.4 Invalid frames

A frame is not started if it has invalid settings. Invalid settings are:

- Start address is bigger than end address in y direction.
- Start address is bigger than end address in x direction.
- Start address and/ or end address out of range in y direction.
- Start address and/ or end address out of range in x direction.
- Integration time setting is 0

If invalid settings are set through a register upload, the next frame is not started and the sensor returns to idle state.

## 7.5 SPI programming

The register block contains an SPI register interface and the array of registers that are used for the chip programmability. Each register is 8-bit wide and can be individually addressed for read and write.

Data is always captured on the rising edge of SPI\_CLK. When reading data from the sensor, the sensor launches data after the rising edge of SPI\_CLK. It shall be captured on the next rising edge of SPI\_CLK.

Because the SPI clock is internally sampled by the master clock, it should be 4x slower than the input master clock. This means that for a 30 MHz master clock, the SPI clock frequency is 7.5MHz. The edges of the SPI clock should coincide with the falling edges of the master clock.

Also note that the master clock input should always be running when doing a SPI transfer.

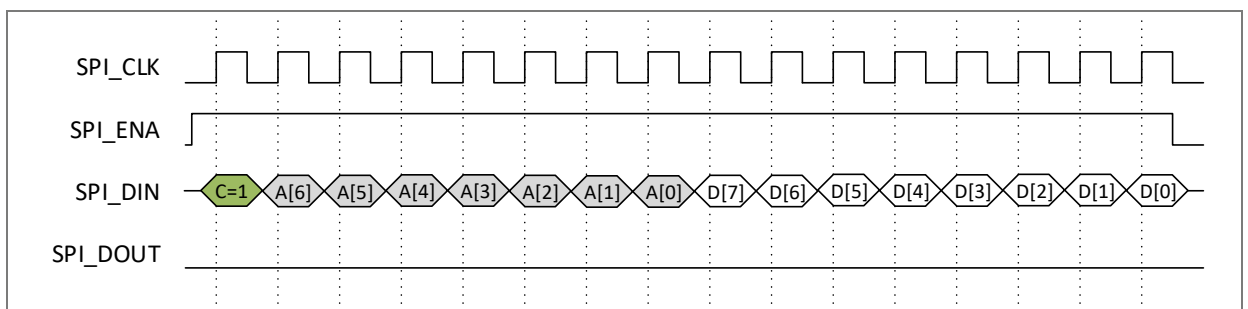
The SPI I/O's will not be tri-stated when not active.

### 7.5.1 SPI write

Data bits are written at each rising edge of the SPI clock (SPI\_CLK). The control bit that is clocked in first on the SPI\_DIN line is used to indicate a write or read access cycle.

In case this control bit is '1', the data bits are written into the on-chip registers as described above.

Figure 19: SPI write timing



### 7.5.2 SPI read

When the control bit is '0', the address bits are clocked in. The data bits on the SPI\_DIN bus are ignored. The data bits in the on-chip register indicated by the address bits are clocked out (SPI\_DOUT) at each falling edge of the clock with a fixed delay of 75ns from the last falling SPI clock edge of the address. Therefore it is recommended to sample the read out bytes in at the falling SPI clock edge.

If SPI\_ENA is made low, the SPI logic immediately resets to an idle state. All transferred bits during the active transfer will be lost. When writing and/or reading multiple registers sequentially, it is allowed to keep SPI\_ENA high in-between two transfers. Doing so allows you to continuously read/write data, without a time gap between transfers.

Figure 20: SPI read timing

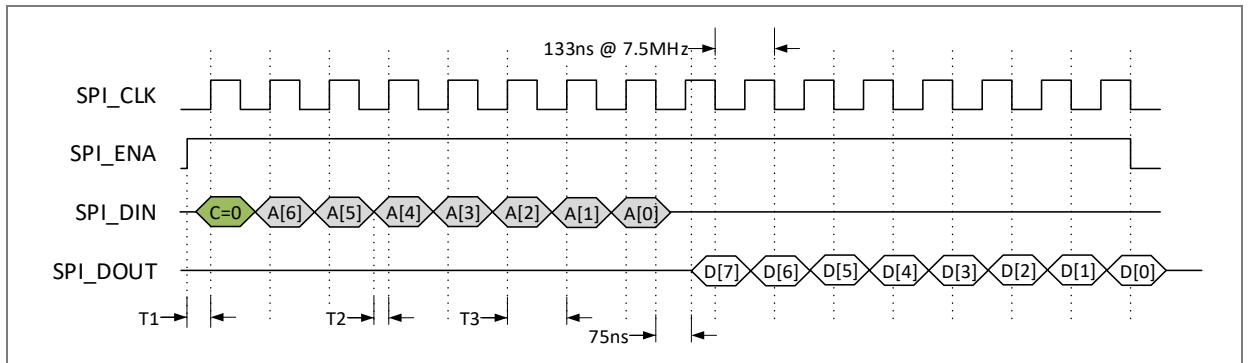


Table 12: SPI reading timing

Time	Description	Requirement
T1	spi_ena setup time before rising edge of spi_clk	Min 0.5x spi_clk period
T2	spi_din setup time before rising edge of spi_clk	Min 0.25x spi_clk period
T3	SPI clock period	Min 4x master clock period

## 7.6 Reading out the sensor

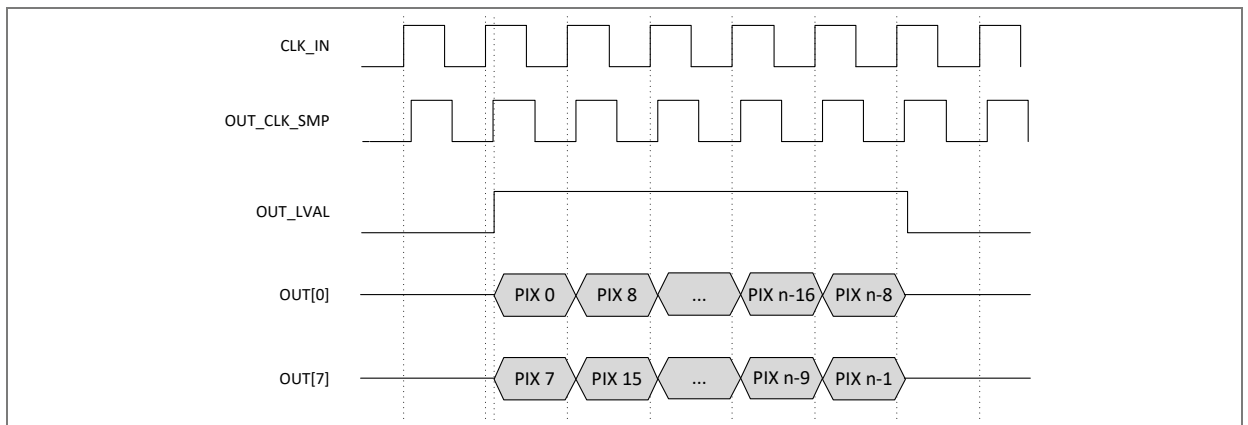
### 7.6.1 Analog data output

The CHR71000 image sensor has 16 internal output channels which are multiplexed to 8 parallel outputs (OUT\_0 to OUT\_7).

### 7.6.2 Timing of chip outputs

There are two digital outputs available that assist frame grabbing. The output OUT\_LVAL indicates when valid pixel information is available at the outputs (see Figure 21). The output OUT\_CLK\_SMP is a sampling clock with the same frequency as the master input clock. This signal can be used to drive external ADC's to ensure correct signal sampling.

Figure 21: Timing of OUT\_CLK\_SMP and OUT\_LVAL signals



The OUT\_LVAL signal is only pulsed when using the internal sequencer. If the sequencer is disabled, it will be '0' continuously.

The output signal OUT\_LVAL can be delayed in steps of 1 master clock cycle. This could be used to incorporate the delay of the data path external to the sensor in the timing of OUT\_LVAL. The register for this delay value is register 17 (reg\_del\_lval).

When using external timing, you can use the CLK\_Y, SYNC\_Y\_READ and the SYNC\_X pulses to know when data is being output. The data read out starts 4 clock pulses after SYNC\_X.

### 7.6.3 Output gain and offset

The gain of the on-chip output amplifier is selectable through the SPI register settings. The gain varies linearly between 1 and 3.5 in 16 steps (4 bits). Up to gain setting 8, the gain increases by approximately 10-12 % for successive settings. From setting 9 onwards, the gain increases by about 20-22 % for successive settings. Figure 22 shows the gain values for the different gain register settings.

Besides the gain, also the offset level of each channel can be programmed. This allows balancing the random offsets of the different internal channels. Internally, the CHR71000 uses 16 analog channels (multiplexed to 8 outputs). That is why 16 offset registers are programmable over SPI (registers 64 – 87). The output buffer has been designed to nominally drive a 20 pF capacitive load at nominal 30 Mpixels/s readout rate (per output). The polarity of the output signal is positive video (dark pixel signals low, bright pixel signals high).

So, the analog output swing depends on the gain and offset settings. You can see the different levels and swing in Figure 23.

Figure 22: PGA setting vs. actual PGA gain

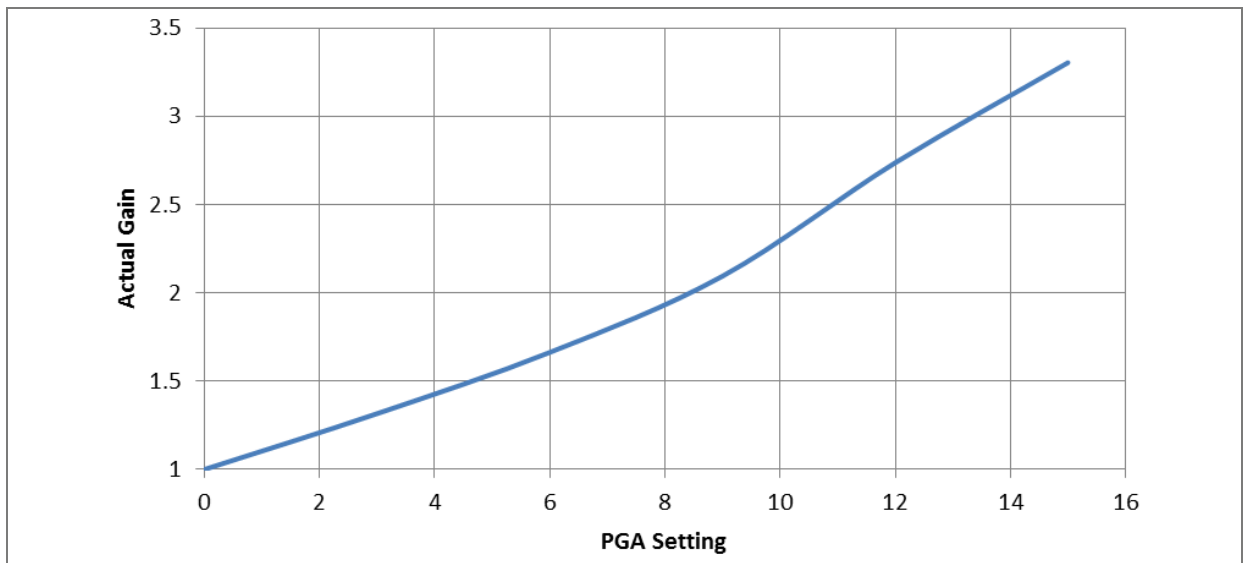
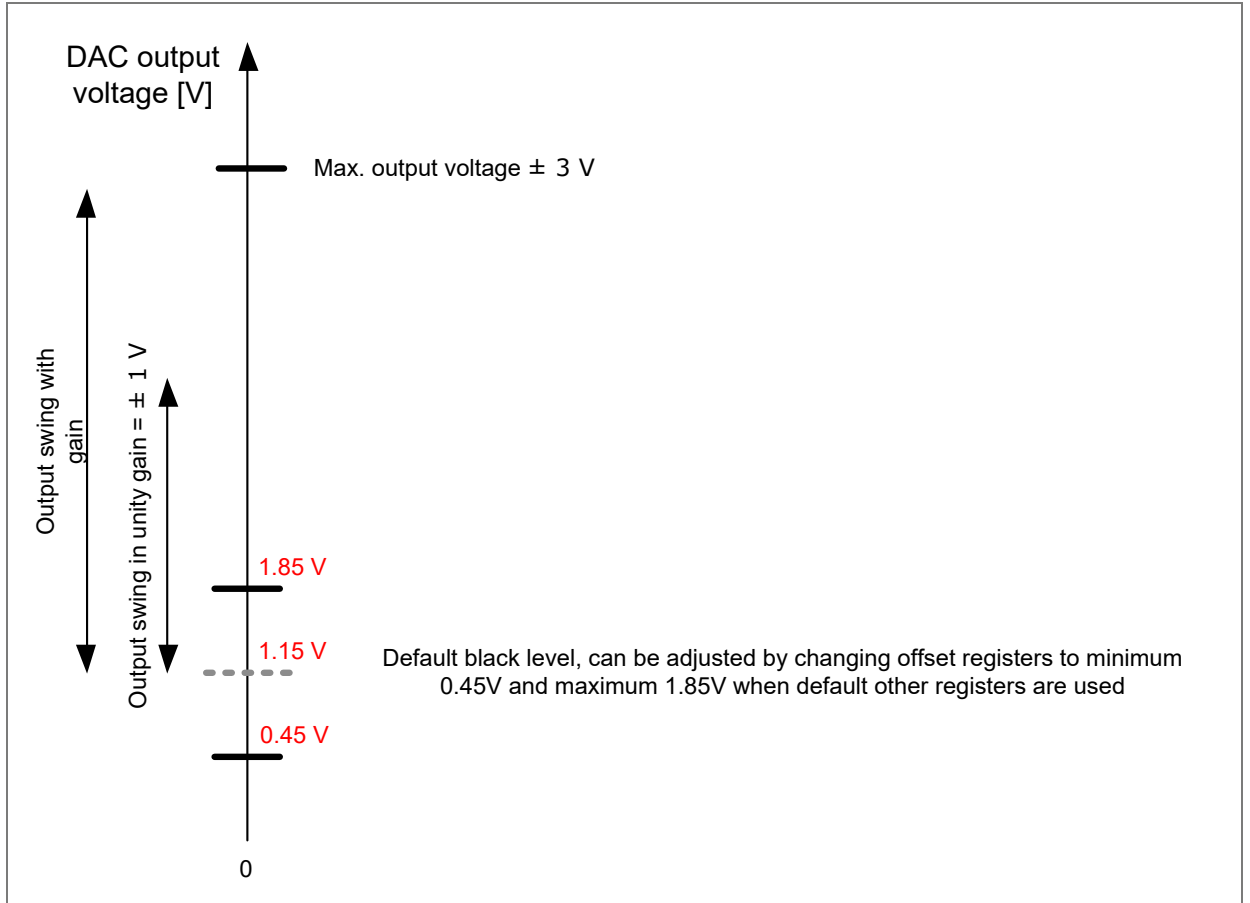


Figure 23: Analog output swing



## 8 Register description

### 8.1 Register overview

The next table shows the register map of the sensor.

The first column of the table gives the address that needs to be uploaded during an SPI transfer to interface with the register. Every register address represents 8 register bits. The second column of the table lists which of the 8 bits of the address are used by the register. The last column contains the value the register should be set to after boot up or reset. They can differ from the default startup value of the register.

A number of registers is reserved for internal use only.

Table 13: Register overview

Addr	Bits	Name	Description	Default	Recommended
0	[7:0]	reg_addr_x_start[7:0]	Start address in x direction	1	1
1	[7:0]	reg_addr_x_end[7:0]	End address in x direction	114	114
2	[7:0]	reg_addr_x_step[7:0]	Step of moving window in x direction	0	0
3	[1:0]	reg_addr_x_start[9:8]	MSB of address setting	0	0
	[3:2]	reg_addr_x_end[9:8]	MSB of address setting	2	2
	[5:4]	reg_addr_x_step[9:8]	MSB of address setting	0	0
4	[7:0]	reg_addr_y_start[7:0]	Start address in y direction	1	1
5	[7:0]	reg_addr_y_end[7:0]	End address in y direction	120	120
6	[7:0]	reg_addr_y_step[7:0]	Step of moving window in y direction	0	0
7	[1:0]	reg_addr_y_start[9:8]	MSB of address setting	0	0
	[3:2]	reg_addr_y_end[9:8]	MSB of address setting	3	3
	[5:4]	reg_addr_y_step[9:8]	MSB of address setting	0	0
8	[7:0]	reg_inte_time[7:0]	Set integration time	181	181
9	[7:0]	reg_inte_time[15:8]	MSB of integration time	27	27
10	[7:0]	reg_inte_time[23:16]	MSB of integration time	0	0
11	[7:0]	reg_nrof_frames[7:0]	Set number of frames in burst	1	1
12	[7:0]	reg_nrof_frames[15:8]	MSB of number of frames in burst	0	0
13	[0]	reg_seq_enable	Enable internal sequencer	0	0
	[1]	reserved	/	0	0
	[2]	reserved	/	0	0
	[3]	reserved	/	1	1

Addr	Bits	Name	Description	Default	Recommended
	[4]	reg_sub_y	Enable sub-sampling in y direction	0	0
	[5]	reserved	/	0	0
	[6]	reserved	/	0	0
14	[7:0]	reg_rot_sample[7:0]		60	60
15	[7:0]	reg_rot_transfer[7:0]		30	30
16	[7:0]	reg_rot_prech[7:0]		2	2
17	[3:0]	reg_del_lval	Delay pulse on OUT_LVAL	1	1
18	[3:0]	reg_pga_gain[3:0]	Gain settings for amplifiers	0	0
18	[4]	reg_pga_gain_uni		0	0
18	[5]	reg_pga_gain_evn		0	0
32	[7:0]	reg_pol[7:0]		255	255
33	[4:0]	reg_pol[12:8]		31	31
33	[5]	reg_pol_amp_phase		1	1
33	[6]	reg_pol_amp_rot		1	1
33	[7]	reg_pol_x_left		1	1
34	[7:0]	reg_rot_clk_y_1[7:0]		3	3
35	[7:0]	reg_rot_clk_y_2[7:0]		1	1
36	[7:0]	reg_rot_prech_nov_1[7:0]		0	0
37	[7:0]	reg_rot_prech_nov_2[7:0]		0	0
38	[7:0]	reg_rot_prech_nov_3[7:0]		1	1
39	[7:0]	reg_rot_sample_nov_1[7:0]		4	<b>14</b>
40	[7:0]	reg_rot_sample_nov_2[7:0]		1	1
41	[7:0]	reg_rot_sample_nov_3[7:0]		58	<b>46</b>
42	[7:0]	reg_rot_transfer_nov_1[7:0]		1	1
43	[7:0]	reg_rot_reset_nov_1[7:0]		0	<b>1</b>
44	[7:0]	reg_rot_sync_x_nov_1[7:0]		0	<b>1</b>
45	[1:0]	reg_bist_start[1:0]		0	0
45	[3:2]	reg_bist_done[1:0]		/	/
46	[4:0]	reg_bist_error[4:0]		/	/
47	[0]	reg_pol_rst_x		1	1
63	[7:0]	reg_revision[7:0]	Revision number of chip	1	1
64	[7:0]	reg_offset_0[7:0]	DAC offset of even pixels in channel 0	0	0
65	[7:0]	reg_offset_1[7:0]	DAC offset of odd pixels in channel 0	0	0
66	[3:0]	reg_offset_0[11:8]	MSB of DAC offset	8	8

Addr	Bits	Name	Description	Default	Recommended
66	[7:4]	reg_offset_1[11:8]	MSB of DAC offset	8	8
67	[7:0]	reg_offset_2[7:0]	DAC offset of even pixels in channel 1	0	0
68	[7:0]	reg_offset_3[7:0]	DAC offset of odd pixels in channel 1	0	0
69	[3:0]	reg_offset_2[11:8]	MSB of DAC offset	8	8
69	[7:4]	reg_offset_3[11:8]	MSB of DAC offset	8	8
70	[7:0]	reg_offset_4[7:0]	DAC offset of even pixels in channel 2	0	0
71	[7:0]	reg_offset_5[7:0]	DAC offset of odd pixels in channel 2	0	0
72	[3:0]	reg_offset_4[11:8]	MSB of DAC offset	8	8
72	[7:4]	reg_offset_5[11:8]	MSB of DAC offset	8	8
73	[7:0]	reg_offset_6[7:0]	DAC offset of even pixels in channel 3	0	0
74	[7:0]	reg_offset_7[7:0]	DAC offset of odd pixels in channel 3	0	0
75	[3:0]	reg_offset_6[11:8]	MSB of DAC offset	8	8
75	[7:4]	reg_offset_7[11:8]	MSB of DAC offset	8	8
76	[7:0]	reg_offset_8[7:0]	DAC offset of even pixels in channel 4	0	0
77	[7:0]	reg_offset_9[7:0]	DAC offset of odd pixels in channel 4	0	0
78	[3:0]	reg_offset_8[11:8]	MSB of DAC offset	8	8
78	[7:4]	reg_offset_9[11:8]	MSB of DAC offset	8	8
79	[7:0]	reg_offset_10[7:0]	DAC offset of even pixels in channel 5	0	0
80	[7:0]	reg_offset_11[7:0]	DAC offset of odd pixels in channel 5	0	0
81	[3:0]	reg_offset_10[11:8]	MSB of DAC offset	8	8
81	[7:4]	reg_offset_11[11:8]	MSB of DAC offset	8	8
82	[7:0]	reg_offset_12[7:0]	DAC offset of even pixels in channel 6	0	0
83	[7:0]	reg_offset_13[7:0]	DAC offset of odd pixels in channel 6	0	0
84	[3:0]	reg_offset_12[11:8]	MSB of DAC offset	8	8
84	[7:4]	reg_offset_13[11:8]	MSB of DAC offset	8	8
85	[7:0]	reg_offset_14[7:0]	DAC offset of even pixels in channel 7	0	0
86	[7:0]	reg_offset_15[7:0]	DAC offset of odd pixels in channel 7	0	0

Addr	Bits	Name	Description	Default	Recommended
87	[3:0]	reg_offset_14[11:8]	MSB of DAC offset	8	8
87	[7:4]	reg_offset_15[11:8]	MSB of DAC offset	8	8
88	[5:0]	reg_dac_high[5:0]	Internal DAC high setting	48	<b>52</b>
89	[5:0]	reg_dac_low[5:0]	Internal DAC low setting	16	<b>12</b>
90	[5:0]	reg_rblank_ref[5:0]	Internal reference voltage setting	32	<b>26</b>
91	[5:0]	reg_clamp[5:0]	Clamping circuit in output stage	63	63
92	[7:0]	reg_stby[7:0]	Standby register	0	0
93	[3:0]	reg_clk_delay[3:0]	Clock delay for sample signal output stage	5	<b>0</b>
	[4]	reg_prebuf_en	Mux buffer before output stage	1	<b>0</b>
	[5]	reg_bgap_on	Internal bandgap reference	1	1
	[6]	reg_separate_mux	Separate multiplexer bus lines	1	1
94	[3:0]	reg_pw_ctr_coldriv[3:0]	Current bias column drivers	8	<b>14</b>
	[7:4]	reg_pw_ctr_pixcds[3:0]	Current bias column amp CDS stage	8	<b>14</b>
95	[3:0]	reg_pw_ctr_colbias[3:0]	Current bias column bus (ctu)	8	<b>0</b>
	[7:4]	reg_pw_ctr_colpc[3:0]	Current bias column bus (precharge)	10	<b>15</b>
96	[3:0]	reg_pw_ctr_driv[3:0]	Current of the output buffers	8	<b>1<sup>(1)</sup></b>
	[7:4]	reg_pw_ctr_pga[3:0]	Current bias output amp CDS/PGA stage	8	<b>8<sup>(2)</sup></b>
97	[3:0]	reg_clk_delay_clk_smp[3:0]	Delay of clk_smp		<sup>(3)</sup>
125	[0]	reg_latch_temp_data	Temperature sensor latch		
126	[7:0]	reg_temperature[7:0]	Temperature sensor read out	0	0
127	[7:0]	reg_temperature[15:8]	Temperature sensor read out	0	0

- (1) System dependent: this depends on the output load of the sensor in the camera, the higher the load, the higher this value should be at the expense of power consumption. Increasing the current of the output buffers will increase the slew rate of the outputs. This can be used to adapt the sensor outputs to the receiver systems input capacitance.
- (2) Testing was done with setting 14, setting 1 shows no visible degradation.
- (3) This register can be used to fine-tune the output clock delay for your specific receiver (ADC) to the data. The delay can be set between 0° - 180°.

The registers reg\_revision[7:0] and reg\_temperature[15:0] are read-only registers. A write operation to one of these registers will not change their contents.

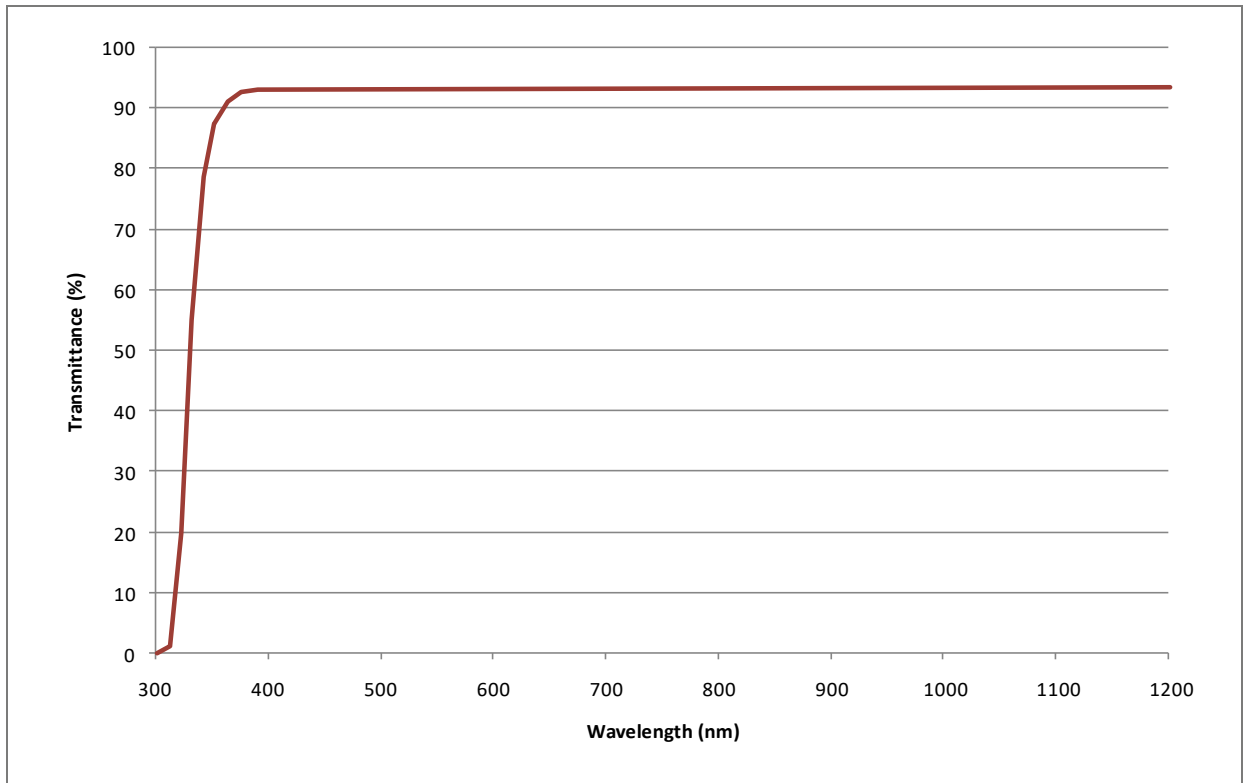
All addresses that are not mentioned in this list are reserved and may not be overwritten.

## 9 Application information

### 9.1 Cover glass

The CHR71000 image sensor is available with a regular D263 glass lid. See the transmittance curve of this glass below.

Figure 24: D263 transmittance curve

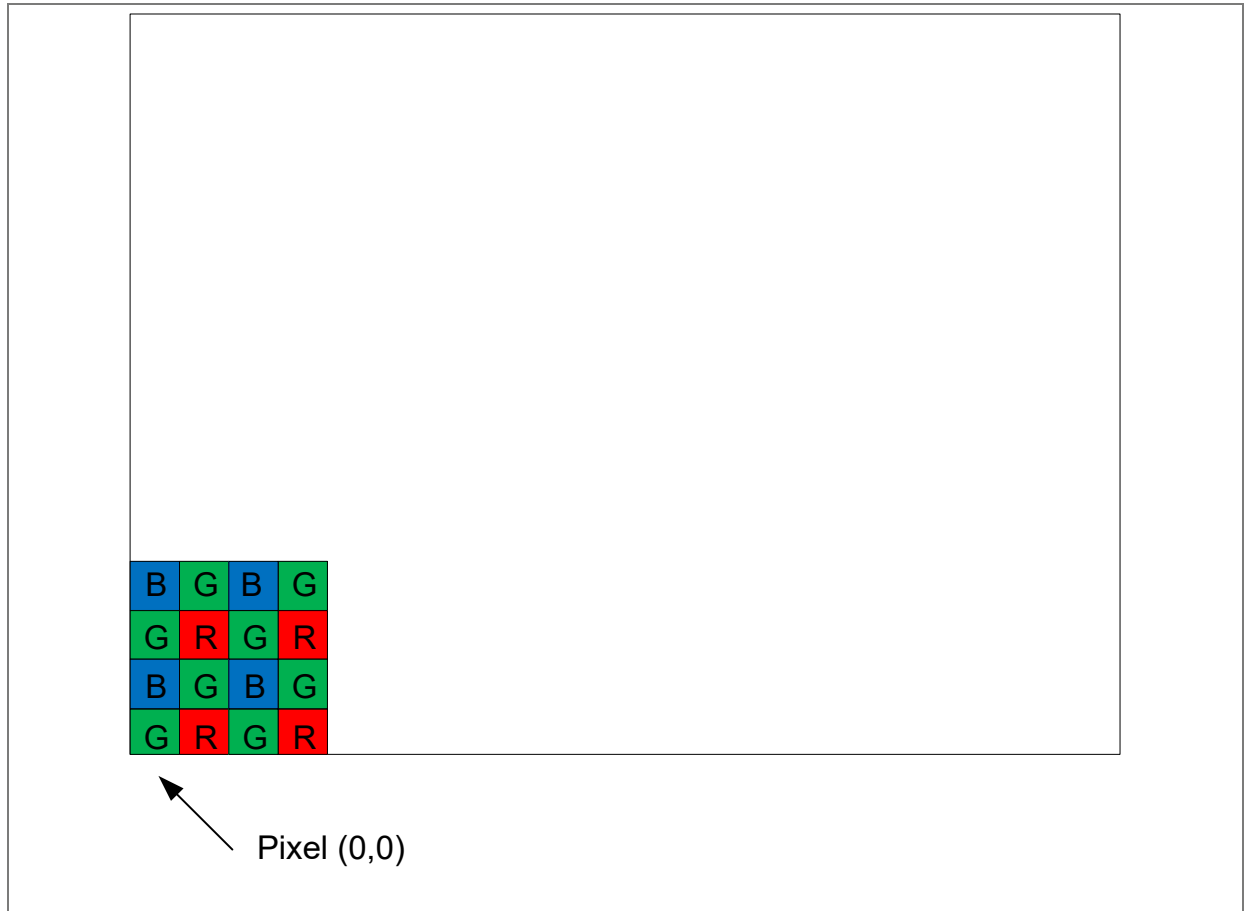


Both types of glass have an AR coating with a reflectance of 0.5% at 500nm.

## 9.2 Color filter

A RGB Bayer pattern is used on the CHR71000 image sensor. The order of the RGB filter can be found in the drawing below.

Figure 25: RGB bayer pattern order

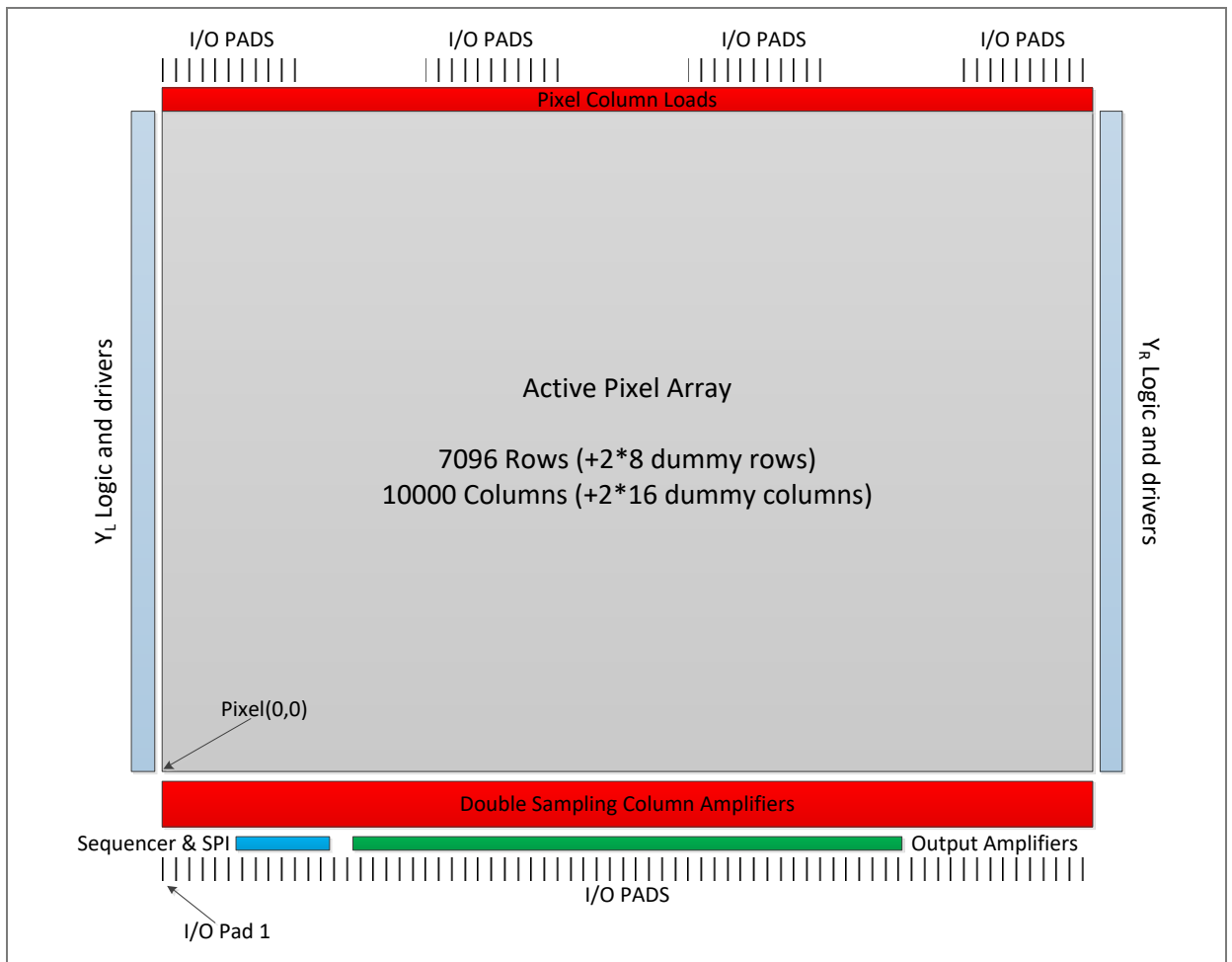




## 10.2 Sensor floor plan

Figure 27 shows the sensor floor plan. The pixel array is centered in the horizontal direction. Pixel (0, 0) is at the bottom left position. Bond pad 1 is also situated at the bottom left. The numbering of the bond pads is counterclockwise.

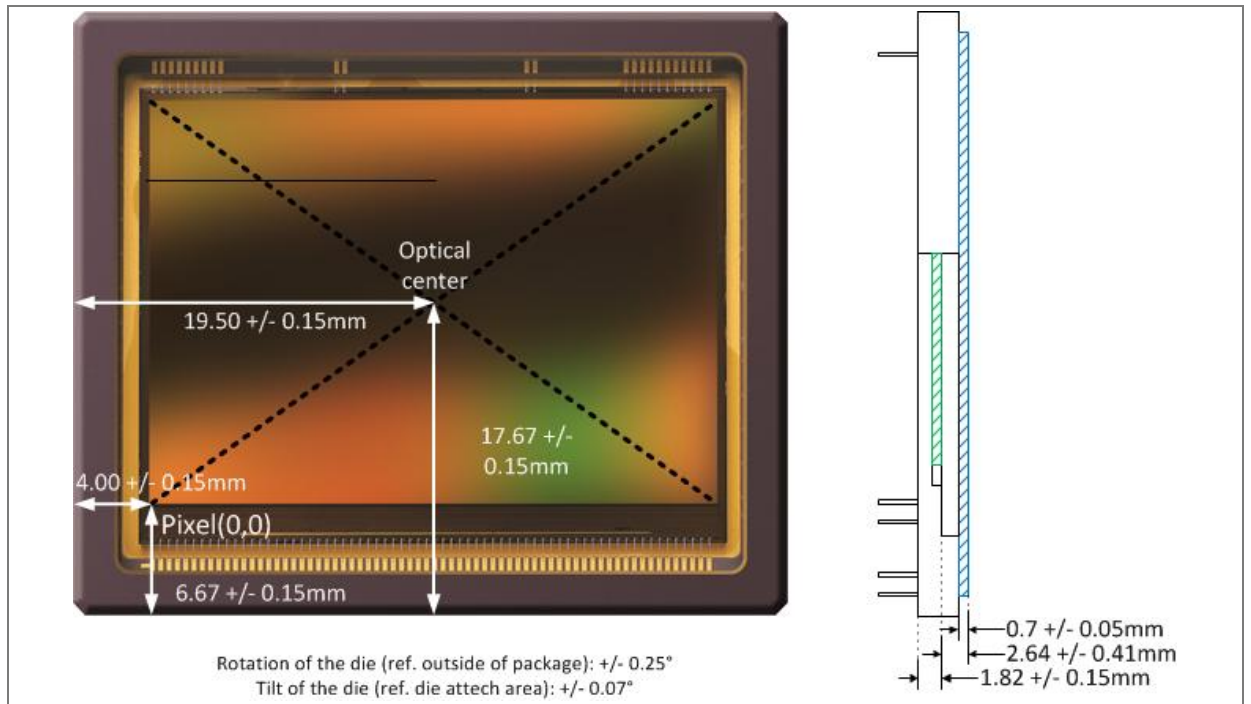
Figure 27: Floor plan of the sensor



### 10.3 Assembly drawing

The figure below shows the assembly of the CHR71000 image sensor die inside the ceramic package.

Figure 28: Assembly drawing



(1) All dimensions are in mm

# 11 Soldering & storage information

Image sensors with filter arrays (CFA) and micro-lens are especially sensitive to high temperatures. Prolonged heating at elevated temperatures may result in deterioration of the performance of the sensor. Best solution will be flow soldering or manual soldering of a socket (through hole or BGA) and plug in the sensor at latest stage of the assembly/test process. The BGA solution allows more flexibility for the routing of the camera PCB.

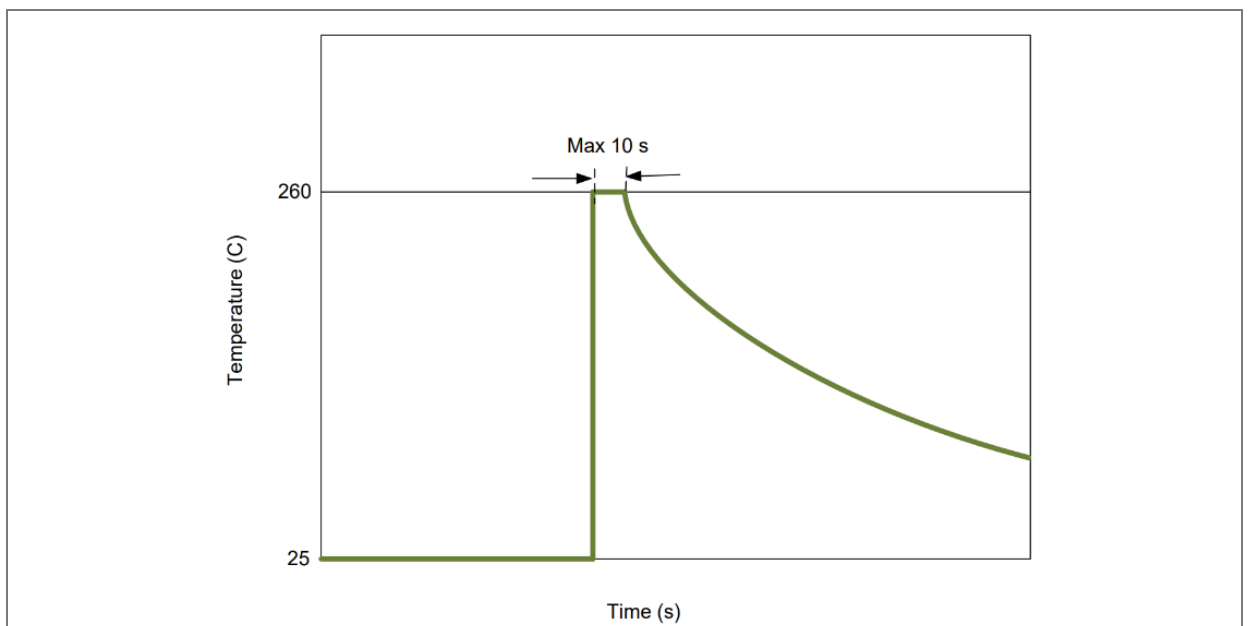
## 11.1 Manual soldering

Use partial heating method and use a soldering iron with temperature control. The soldering iron tip temperature is not to exceed 350°C with 270°C maximum pin temperature, 2 seconds maximum duration per pin. Avoid global heating of the ceramic package during soldering. Failure to do so may alter device performance and reliability.

## 11.2 Wave soldering

Wave soldering is possible but not recommended. Solder dipping can cause damage to the glass and harm the imaging capability of the device. See the figure below for the wave soldering profile.

Figure 29: Wave solder profile



## 11.3 Storage

Image sensors should be stored under the following conditions:

- Dust free
- Temperature 20°C to 40°C
- Humidity between 30% and 60%
- Avoid radiation, electromagnetic fields, ESD, mechanical stress

## 11.4 Additional information

### 11.4.1 ESD

The following are the recommended minimum ESD requirements when handling image sensors:

- Ground workspace (tables, floors...)
- Ground handling personnel (wrist straps, special footwear...)
- Minimize static charging (control humidity, use ionized air, wear gloves...)

### 11.4.2 Glass cleaning

When cleaning of the cover glass is needed we recommend the following two methods.

- Blowing off the particles with ionized nitrogen.
- Wipe clean using IPA (isopropyl alcohol) and ESD protective wipes.

### 11.4.3 Excessive light

Excessive light falling on the sensor can cause heating up the micro lenses and color filters. This heat can cause deforming of the lenses and/or deterioration of the lenses and color filters by making them more opaque, increasing the heat up even more. Avoid shining high intensity light upon the sensors for extended periods of time. In case of lasers, they can cause heat up but can also damage the silicon die itself.

## 12 Revision information

Document status	Product status	Definition
Product Preview	Pre-development	Information in this datasheet is based on product ideas in the planning phase of development. All specifications are design goals without any warranty and are subject to change without notice
Preliminary Datasheet	Pre-production	Information in this datasheet is based on products in the design, validation or qualification phase of development. The performance and parameters shown in this document are preliminary without any warranty and are subject to change without notice
Datasheet	Production	Information in this datasheet is based on products in ramp-up to full production or full production which conform to specifications in accordance with the terms of ams-OSRAM AG standard warranty as given in the General Terms of Trade

### Other definitions

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Changes from previous released version to current revision v2-01	Page
<b>Changes from v1-00 to v2-00</b>	
Datasheet contents transferred to the new ams OSRAM template	
<b>Changes from v2-00 to v2-01</b>	
Updated all instances of "CHR70000" to "CHR71000"	

- Page and figure numbers for the previous version may differ from page and figure numbers in the current revision.
- Correction of typographical errors is not explicitly mentioned.

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